

23 December 1980

## SPECIFICATION

MICROCIRCUITS, LINEAR, CMOS, HIGH LEVEL  
ANALOG SWITCH WITH DRIVER,  
MONOLITHIC SILICON

This specification is approved for use by all Departments and Agencies of the Department of Defense.

## 1. SCOPE

1.1 Scope. This specification covers the detail requirements for silicon, CMOS monolithic, analog switches. Three product assurance classes and a choice of case outline and lead finish are provided for each type and are reflected in the complete part number.

1.2 Part number. The part number shall be in accordance with MIL-M-38510.

1.2.1 Device type. The device type shall be as follows:

<u>Device type</u>	<u>Circuit</u>
01	One-channel, 75 ohm, SPST switch
02	Two-channel, 75 ohm, SPST switch
03	One-channel, 75 ohm, SPDT switch
04	Two-channel, 75 ohm, SPDT switch
05	One-channel, 75 ohm, DPST switch
06	Two-channel, 75 ohm, DPST switch
07	One-channel, 75 ohm, DPDT switch
08	One-channel, 75 ohm, 4PST switch

NOTE: A channel is defined as a driver with associated switches.

1.2.2 Device class. The device class shall be the product assurance level as defined in MIL-M-38510.

1.2.3 Case outline. The case outline shall be designated as follows:

<u>Outline letter</u>	<u>MIL-M-38510, appendix C case outline</u>
A	F-1 (14-lead, 1/4" x 1/4", flat package)
E	D-2 (16-lead, 1/4" x 7/8", dual-in-line)
I	A-2 (10-lead can)

1.3 Absolute maximum ratings:

V <sup>+</sup> - V <sup>-</sup>	- - - - -	33 Vdc
V <sup>+</sup> - V <sub>D</sub>	- - - - -	30 Vdc
V <sub>D</sub> - V <sup>-</sup>	- - - - -	30 Vdc
V <sub>D</sub> - V <sub>S</sub>	- - - - -	±22 Vdc
V <sub>L</sub> - V <sup>-</sup>	- - - - -	33 Vdc
V <sub>L</sub> - V <sub>IN</sub>	- - - - -	30 Vdc
V <sub>L</sub> - V <sub>R</sub>	- - - - -	20 Vdc
V <sub>IN</sub> - V <sub>R</sub>	- - - - -	20 Vdc
V <sub>R</sub> - V <sup>-</sup>	- - - - -	33 Vdc
V <sub>R</sub> - V <sub>IN</sub>	- - - - -	2 Vdc
Current (any terminal except S or D)	- - - - -	30 mA
Storage temperature range	- - - - -	-65 to 150°C
Lead temperature (soldering, 60 seconds)	- - - - -	300°C
Junction temperature	- - - - -	T <sub>J</sub> = 175°C

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Rome Air Development Center, RBE-2, Griffiss AFB, NY 13441, by using the self-addressed Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

1.4 Recommended operating conditions:

+V <sub>CC</sub>	- - - - -	+15 Vdc
-V <sub>CC</sub>	- - - - -	-15 Vdc
V <sub>R</sub>	- - - - -	0 Vdc
V <sub>L</sub>	- - - - -	5 Vdc
Case operating temperature range	- - -	-55 to 125°C

1.5 Power and thermal characteristics.

<u>Package</u>	<u>Case Outline</u>	<u>Maximum allowable power dissipation</u> 1/	<u>Maximum</u> $\theta_{J-C}$ 2/	<u>Maximum</u> $\theta_{J-A}$
14-lead FP	A	350 mW @ T <sub>C</sub> = 125°C	60°C/W	140°C/W
16-lead DIP	E	400 mW @ T <sub>C</sub> = 125°C	35°C/W	120°C/W
10-lead can	I	350 mW @ T <sub>C</sub> = 125°C	40°C/W	140°C/W

## NOTES:

1. All leads welded or soldered to PC board
2. Applies only when T<sub>C</sub> ≥ 75°C.

## 2. APPLICABLE DOCUMENTS

2.1 Issues of documents. The following documents of the issue in effect on date of invitation for bids or request for proposal, form a part of this specification to the extent specified herein.

## SPECIFICATION

## MILITARY

MIL-M-38510 - Microcircuits, General Specification for.

## STANDARD

## MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

(Copies of specifications, standards, drawings, and publications required by contractors in connection with specific procurement functions should be obtained from the procuring activity or as directed by the contracting officer.)

## 3. REQUIREMENTS

3.1 Detail specifications. The individual item requirements shall be in accordance with MIL-M-38510, and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and 1.2.3 herein.

3.2.1 Circuit diagram and terminal connections. The circuit diagram and terminal connections shall be as specified on figure 1.

3.2.2 Schematic circuit. The schematic circuits shall be as specified on figure 2.

3.3 Lead material and finish. The lead material and finish shall be in accordance with MIL-M-38510 (see 6.5).

3.4 Electrical performance characteristics. The electrical performance characteristics in table I apply over the full case ambient temperature range of -55° to 125°C and for supply voltages as indicated in 1.4, unless otherwise specified.

TABLE I. Electrical performance characteristics.

Characteristic	Symbol	Conditions $V_{CC} = \pm 15V$ unless otherwise specified	Temperature	Device type	Limits		Units	
					Min	Max		
Drain - Source "ON" resistance	$R_{DS}$	(See figure 3)	$V_D = -10 V,$	$T_C = -55^\circ C, 25^\circ C$	All	---	75	$\Omega$
			$I_S = 10 mA$	$T_C = 125^\circ C$	All	---	150	
			$V_D = 10 V,$	$T_C = -55^\circ C, 25^\circ C$	All	---	75	
			$I_S = -10 mA$	$T_C = 125^\circ C$	All	---	150	
Channel "ON" leakage current	$I_{D(ON)}$	(See figure 4) (See 3.4.1 for $V_{IN}$ )	$V_S = V_D = 10 V$	$T_C = -55^\circ C, 125^\circ C$	All	-200	200	nA
			$V_S = V_D = -10 V$	$T_C = 25^\circ C$	All	-2	2	
			$V_S = V_D = 10 V$	$T_C = -55^\circ C, 125^\circ C$	All	-200	200	
			$V_S = V_D = -10 V$	$T_C = 25^\circ C$	All	-2	2	
Drain "OFF" leakage current	$I_{D(OFF)}$	(See figure 5) (See 3.4.1 for $V_{IN}$ )	$V_S = -10 V,$	$T_C = -55^\circ C, 125^\circ C$	All	-100	100	
			$V_D = 10 V$	$T_C = 25^\circ C$	All	-1	1	
			$V_S = 10 V,$	$T_C = -55^\circ C, 125^\circ C$	All	-100	100	
			$V_D = -10 V$	$T_C = 25^\circ C$	All	-1	1	
Source "OFF" leakage current	$I_{S(OFF)}$	(See figure 6) (See 3.4.1 for $V_{IN}$ )	$V_S = 10 V,$	$T_C = -55^\circ C, 125^\circ C$	All	-100	100	
			$V_D = -10 V$	$T_C = 25^\circ C$	All	-1	1	
			$V_S = -10 V,$	$T_C = -55^\circ C, 125^\circ C$	All	-100	100	
			$V_D = 10 V$	$T_C = 25^\circ C$	All	-1	1	
Input current, input voltage low	$I_{IL}$	$V_{IN} = 0 V$	(See figure 7)	$T_C = -55^\circ C, 25^\circ C$	All	-1	0	$\mu A$
				$T_C = 125^\circ C$	All	-10	0	
Input current, input voltage high	$I_{IH}$	$V_{IN} = 2.4 V,$ $15 V$	(See figure 7)	$T_C = -55^\circ C, 25^\circ C$	All	0	1	
				$T_C = 125^\circ C$	All	0	10	
Positive supply current	$+I_{CC}$	$V_{IN} = 0 V,$ $15 V$	(See figure 8)	$T_C = -55^\circ C, 25^\circ C$	All	---	10	
Negative supply current	$-I_{CC}$	$V_{IN} = 0 V,$ $15 V$	(See figure 8)	$T_C = 125^\circ C$	All	---	100	
Logic supply current	$+I_L$	$V_{IN} = 0 V,$ $15 V$	(See figure 8)	$T_C = -55^\circ C, 25^\circ C$	All	-10	---	
				$T_C = 125^\circ C$	All	-100	---	

See note at end of table.

TABLE I. Electrical performance characteristics - Continued.

Characteristic	Symbol	Conditions $V_{CC} = \pm 15V$ unless otherwise specified	Temperature	Device type	Limits		Units
					Min	Max	
Reference supply current	$+I_R$	$V_{IN} = 0 V$ , 5 V (See figure 8)	$T_C = -55^\circ C, 25^\circ C$ $T_C = 125^\circ C$	All	-10 -100	--- ---	mA
Turn on time	$t_{on}$	(See figure 9)	$T_C = -55^\circ C$ $T_C = 25^\circ C$ $T_C = 125^\circ C$		---	375 450 550	ns
Turn off time	$t_{off}$	(See figure 9)	$T_C = -55^\circ C$ $T_C = 25^\circ C$ $T_C = 125^\circ C$		---	190 250 400	
Single channel isolation	$V_{ISO}$	(See figure 10) $f = 1 \text{ MHz}$ $V_{GEN} = 1 \text{ Vp-p}$	$T_C = 25^\circ C$		50	---	dB
Crosstalk between channels	$V_{CT}$	(See figure 11) $f = 1 \text{ MHz}$ $V_{GEN} = 1 \text{ Vp-p}$	$T_C = 25^\circ C$		50	---	
Charge transfer error	$V_{CTE}$	(See figure 12) $V_S = GND$	$T_C = 25^\circ C$		---	15	mV
Break-before-make time delay	$t_D$	(See figure 13)	$-55^\circ C \leq T_C \leq 125^\circ C$	03,04, 07	20	---	ns
Driver input capacitance	$C_A$	$V_{IN} = 0 V$ (See 4.4.1d)	$T_C = 25^\circ C$	All	---	6	pF
Switch input capacitance	$C_{IS}$	(See 4.4.1d) (switch off)	$T_C = 25^\circ C$		---	10	
Switch output capacitance	$C_{OS}$	(See 4.4.1d) (switch off)	$T_C = 25^\circ C$		---	10	
Input test voltage	$V_{ZAP}$	$C_1 = 100 \text{ pF}$ $R_2 = 1.5 \text{ k}\Omega$ (See 4.5.3)	$T_C = 25^\circ C$		400	---	V

## NOTE:

1. The listed resistance limits correspond to the following voltage values:

75 $\Omega$   $\pm 9.25 \text{ V}, \pm 6.75 \text{ V}$   
 150 $\Omega$   $\pm 8.50 \text{ V}, \pm 6.0 \text{ V}$  See table III.

3.4.1 Switch operation. The analog switches listed below are guaranteed to turn "on" with either a "low" input ( $V_R \leq V_{IL} \leq 0.8 \text{ V}$ ) or "high" input ( $2.4 \text{ V} \leq V_{IH} \leq V_{IL}$ ) as specified below (see figure 1).

Device types	$V_{IN}$	Channels ON	Channels OFF
01	2.4 Vdc 0.8 Vdc	1	1
02, 05 03	2.4 Vdc 0.8 Vdc	1,2   1 2	1,2   2 1
04	2.4 Vdc 0.8 Vdc	1,2 3,4	3,4 1,2
07	2.4 Vdc 0.8 Vdc	2,3 1,4	1,4 2,3
06, 08	2.4 Vdc 0.8 Vdc	1,2,3,4	1,2,3,4

3.5 Electrical test requirements. The electrical test requirements shall be as specified in table II. The subgroups of table III which constitute the minimum electrical test requirements for screening, qualification, and quality conformance by device class are specified in table II.

TABLE II. Electrical test requirements.

MIL-STD-883 test requirement	Subgroups (see table III)		
	Class S devices	Class B devices	Class C devices
Interim electrical parameters (pre-burn-in) (method 5004)	1	1	None
Final electrical test parameters (method 5004)	1*, 2,3,9	1*,2,3,9	1
Group A test requirements (method 5005)	1,2,3,9,10,11,12***,13,14	1,2,3,9,10,11,12***,13,14	1,2,3,9
Group C end point and group B class S electrical parameters (method 5005)	1,2,3 and table IV delta limits	1 and table IV delta limits	1 and table IV delta limits
Additional electrical subgroups for group C periodic inspections	Not applicable	None	10,11,12,13,14
Group D end point electrical parameters (method 5005)	1,2,3	1	1
Additional electrical subgroups for group D periodic inspections	(4,7)**	(4,7)**	(4,7)**

- \* PDA applies to subgroup 1 (see 4.2d).
- \*\* See 4.4.4b
- \*\*\* See 4.4.1d

3.6 Marking. Marking shall be in accordance with MIL-M-38510. At the option of the manufacturer, marking of the country of origin may be omitted from the body of the microcircuit, but shall be retained on the initial container.

3.7 Microcircuit group assignment. The devices covered by this specification shall be in microcircuit group number 57 (see MIL-M-38510, appendix E).

#### 4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with MIL-M-38510 and methods 5005 and 5007, as applicable, of MIL-STD-883, except as modified herein.

4.2 Screening. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:

- a. Burn-in (method 1015 of MIL-STD-883).
  1. Static test (test condition A) using the circuit shown on figure 14, or equivalent. Ambient temperature ( $T_A$ ) shall be 125°C minimum. Duration for each static test shall be 24 hours minimum for class S devices and 160 hours minimum for class B devices.
  2. Dynamic test (for class S only) (test condition D or E) using the circuit shown on figure 15.  
NOTE: If accelerated high-temperature test conditions are used, the device manufacturer shall ensure that at least 85 percent of the applied voltage is dropped across the device at temperature. The device is not considered functional under accelerated test conditions.
- b. Reverse bias burn-in (method 1015 of MIL-STD-883). Required for classes S and B devices using the circuit shown on figure 14. Ambient temperature ( $T_A$ ) shall be 125°C minimum. Duration for each reverse bias test shall be 24 hours minimum for class S devices and 160 hours minimum for class B devices.
- c. Interim and final electrical parameters shall be as specified in table II herein.
- d. For class S devices, post-dynamic burn-in, or class B devices, post-static burn-in, electrical parameter measurements may, at the manufacturer's option, be performed separately or included in the final electrical parameter measurements.
- e. Percent defective allowable (PDA) - The PDA for class S devices shall be as specified in MIL-M-38510. The PDA is specified as 10 percent for class B devices based on failures from group A, subgroup 1 test after cooldown as final electrical test in accordance with 5004 of MIL-STD-883, and with no intervening electrical measurements. If interim electrical parameter tests are performed prior to burn-in, failures resulting from preburn-in screening may be excluded from the PDA. If interim electrical parameter tests prior to burn-in are omitted, then all screening failures shall be included in the PDA. The verified failures of group A, subgroup 1 after burn-in divided by the total number of devices submitted for burn-in in that lot shall be used to determine the percent defective for that lot, and the lot shall be accepted or rejected based on the PDA for the applicable device class. Those devices whose measured characteristics after burn-in exceed specified electrical parameter limits are defective and shall be removed from the lot.

4.3 Qualification inspection. Qualification inspection shall be in accordance with MIL-M-38510. Inspections to be performed shall be those specified herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).

4.4 Quality conformance inspection. Quality conformance inspection shall be in accordance with MIL-M-38510. Inspections to be performed shall be those specified in method 5005 of MIL-STD-883 and herein for group A, B, C, and D inspections (see 4.4.1 through 4.4.4).

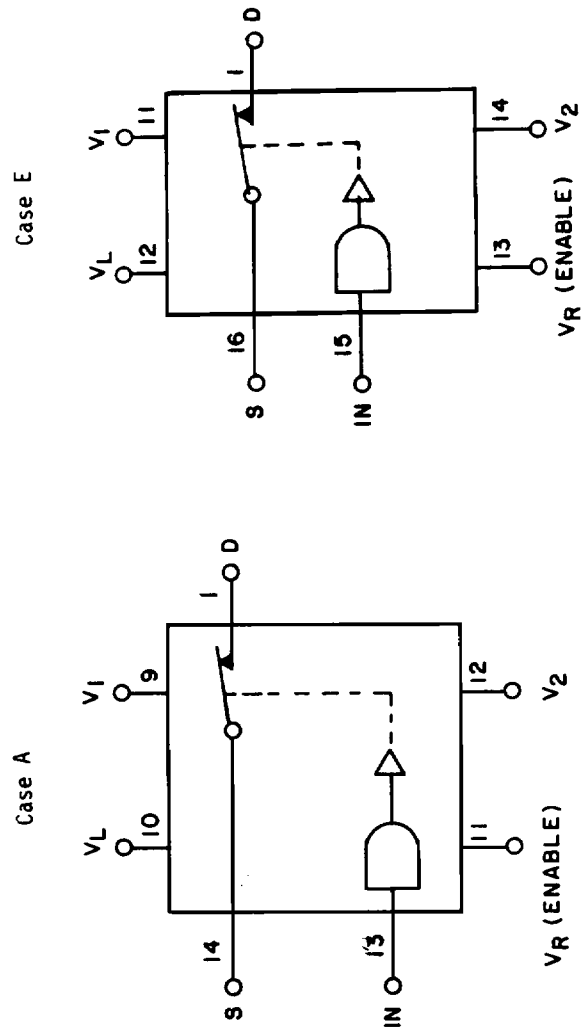
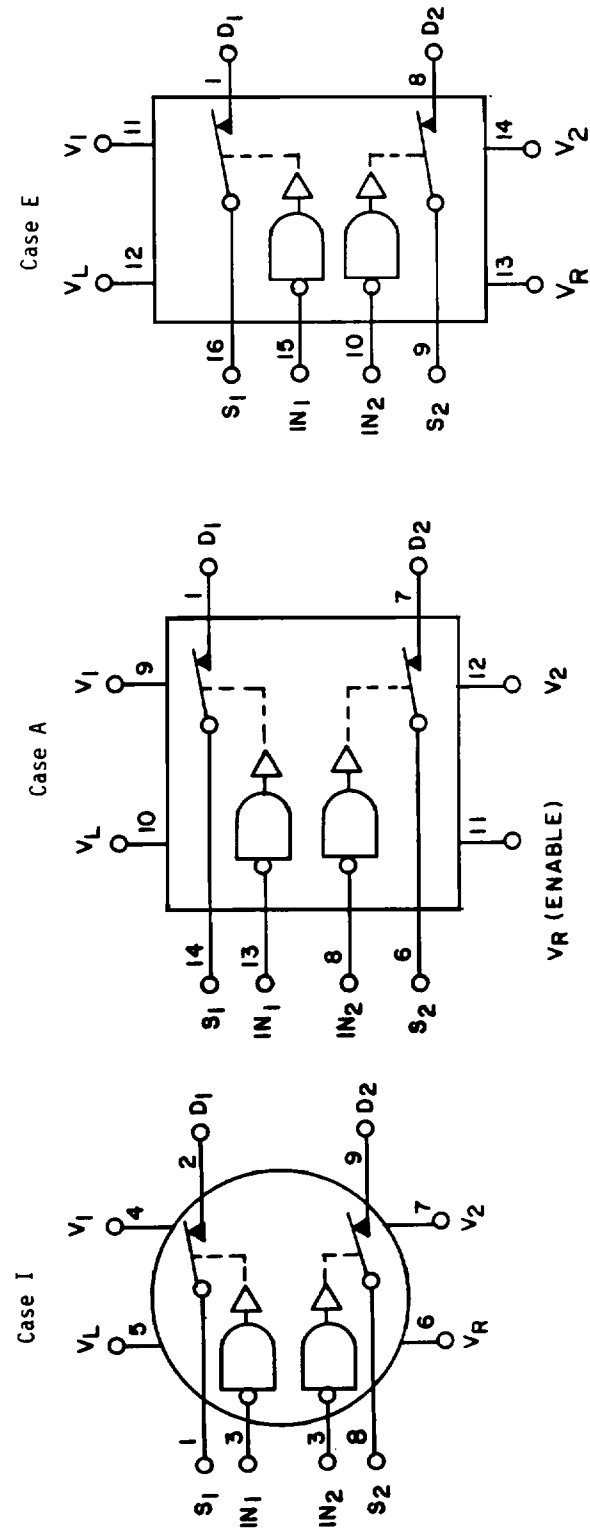
Device type 01Device type 02

FIGURE 1. Terminal connections (see 3.4.1).

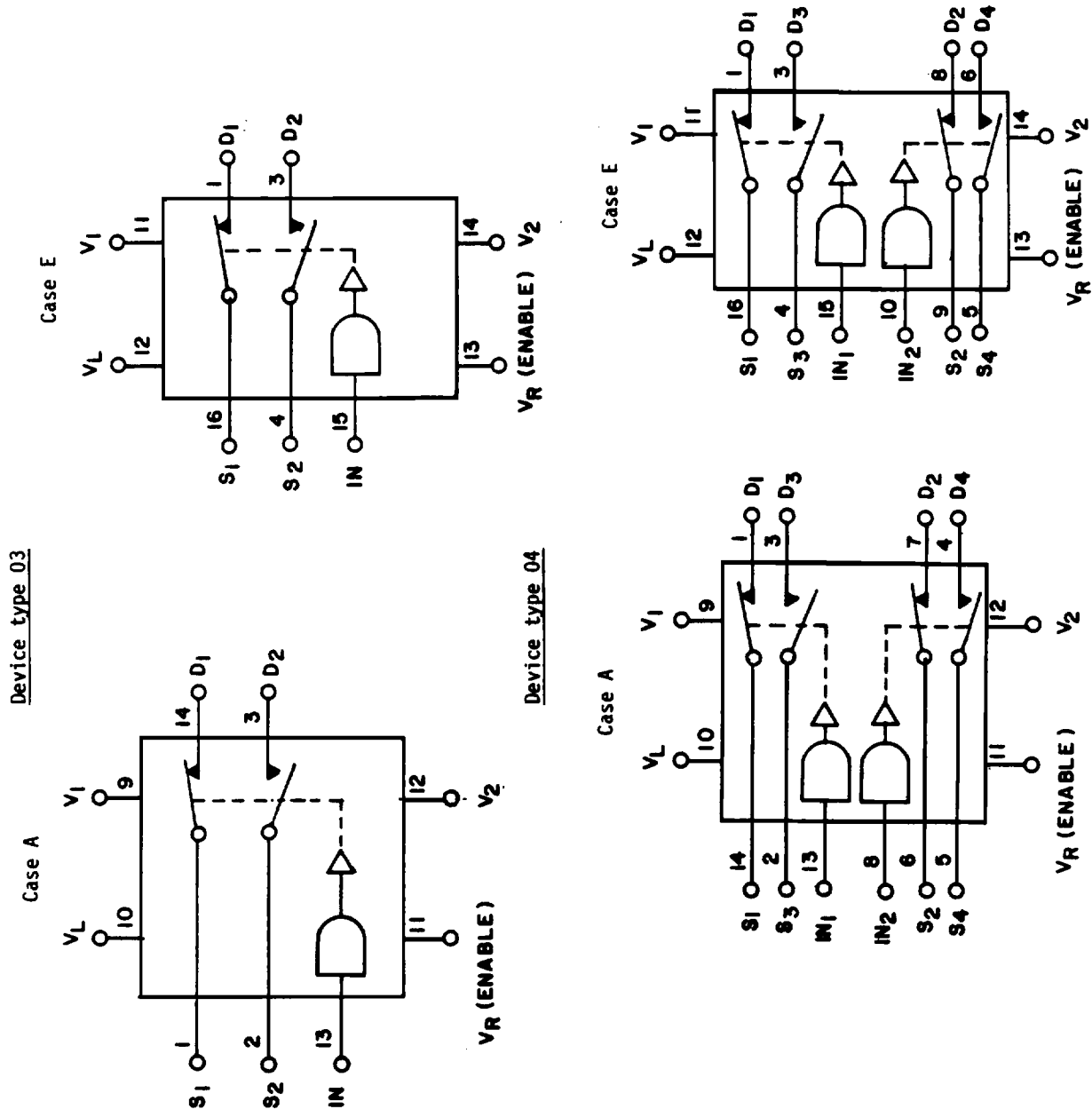


FIGURE 1. Terminal connections (see 3.4.1) - Continued.



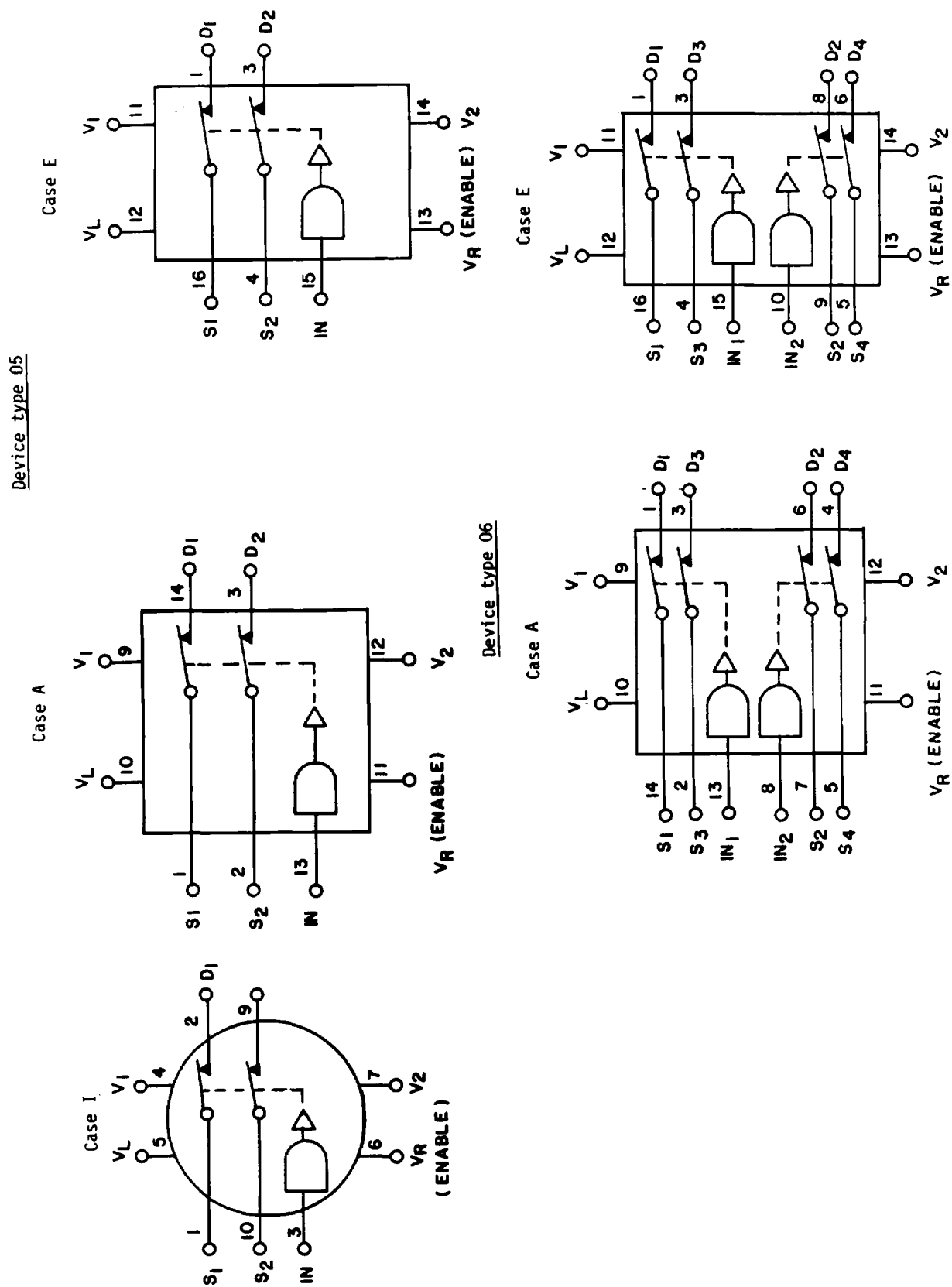
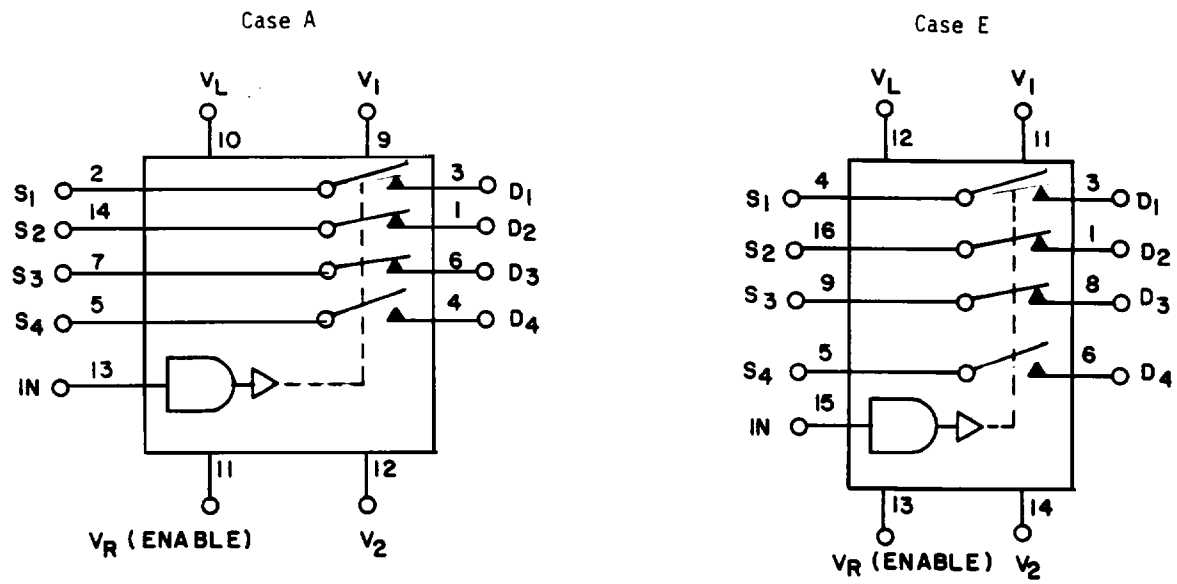


FIGURE 1. Terminal connections (see 3.4.1) - Continued.

## Device type 07



## Device type 08

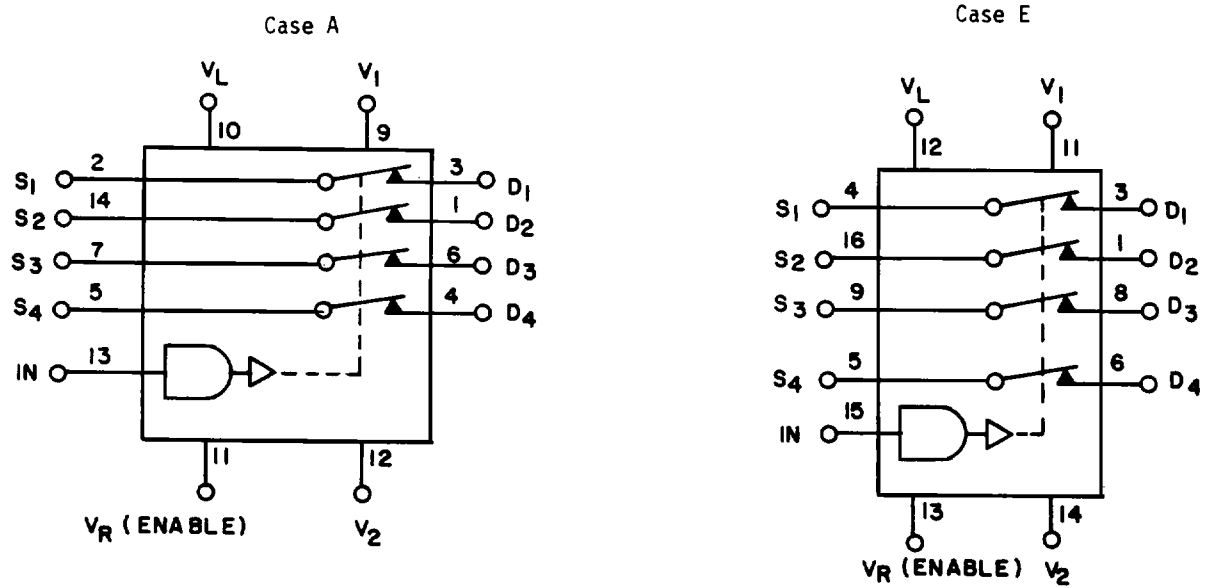


FIGURE 1. Terminal connections (see 3.4.1) - Continued.

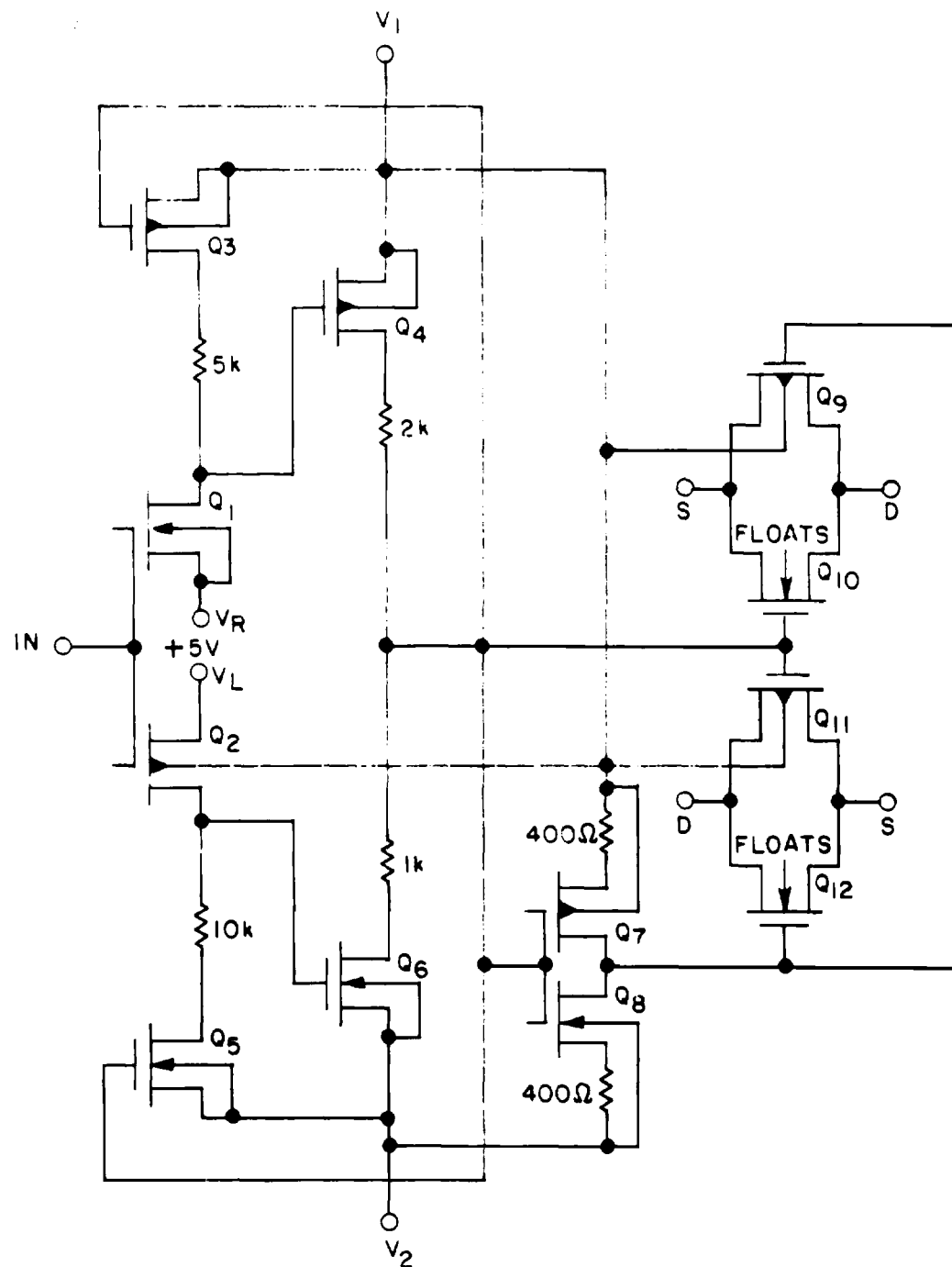
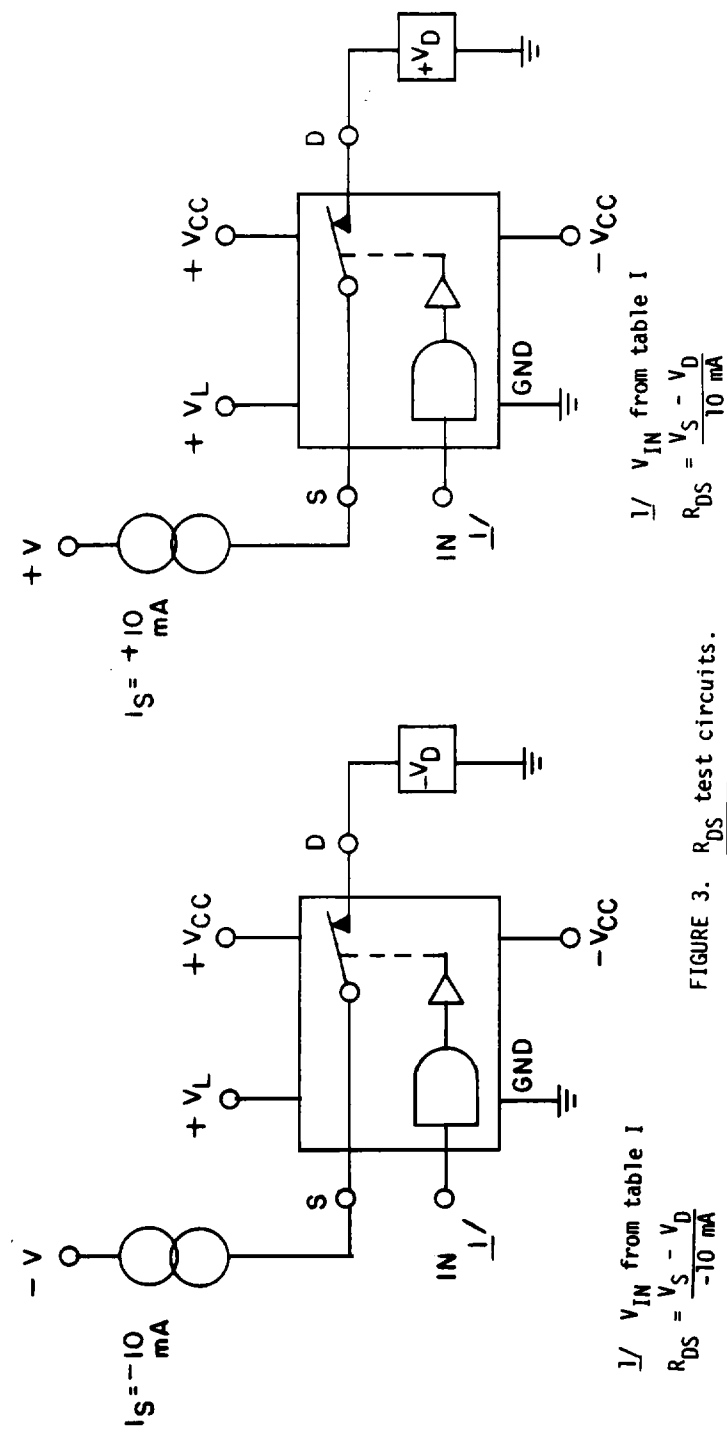
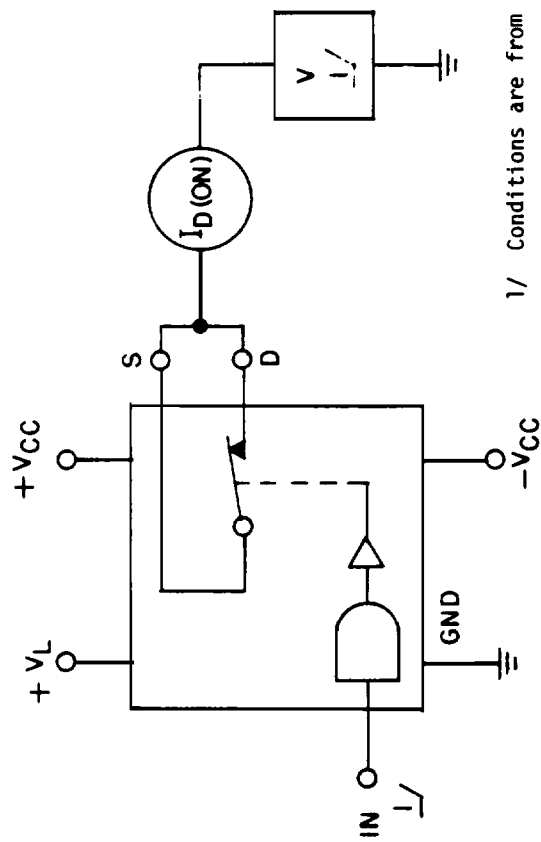
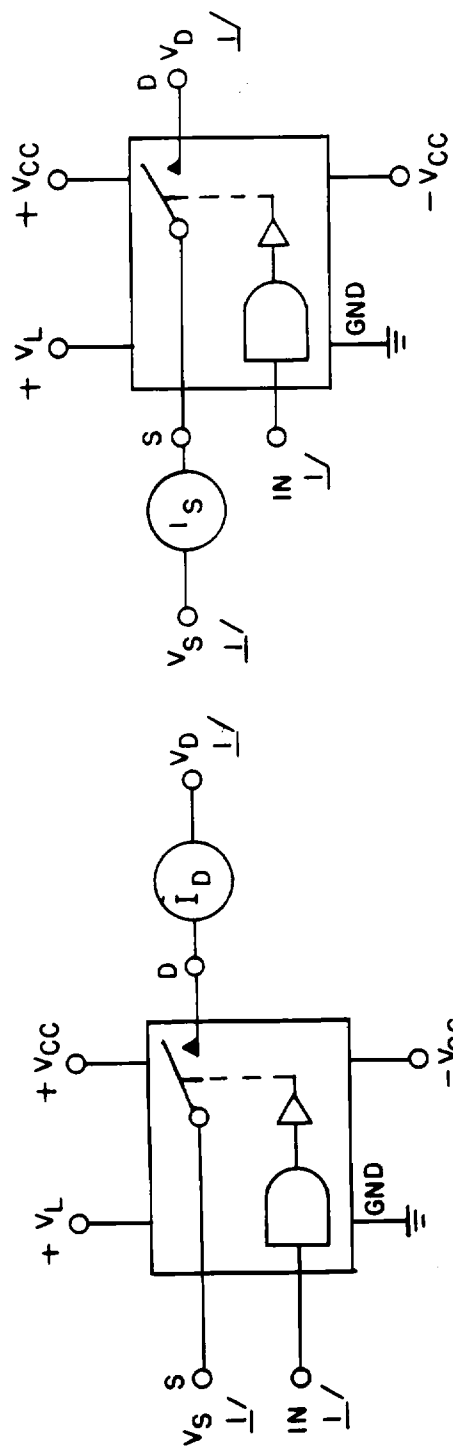


FIGURE 2. Schematic circuits.

FIGURE 3.  $R_{DS}$  test circuits.

1/ Conditions are from table I.

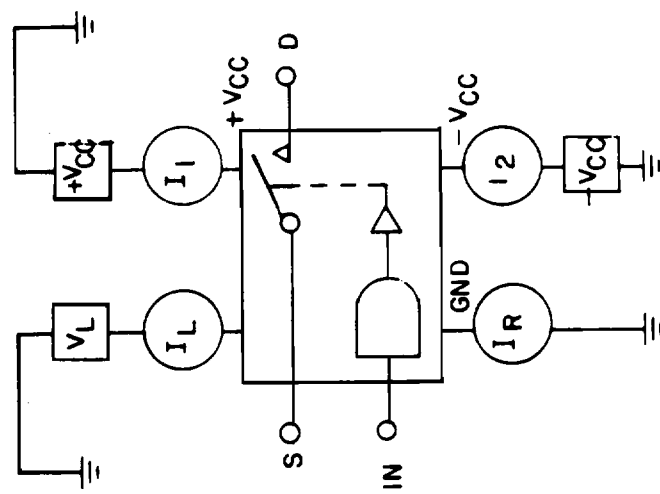
FIGURE 4.  $I_{D(on)}$  test circuit.



$I_I$  Test conditions are from table I.

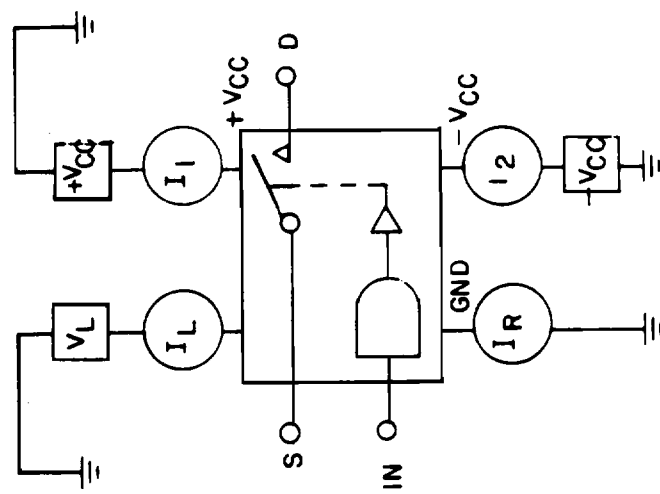
FIGURE 5.  $I_{D(off)}$  test circuit.

FIGURE 6.  $I_{S(off)}$  test circuit.



$I_I$  Test conditions are from table I.

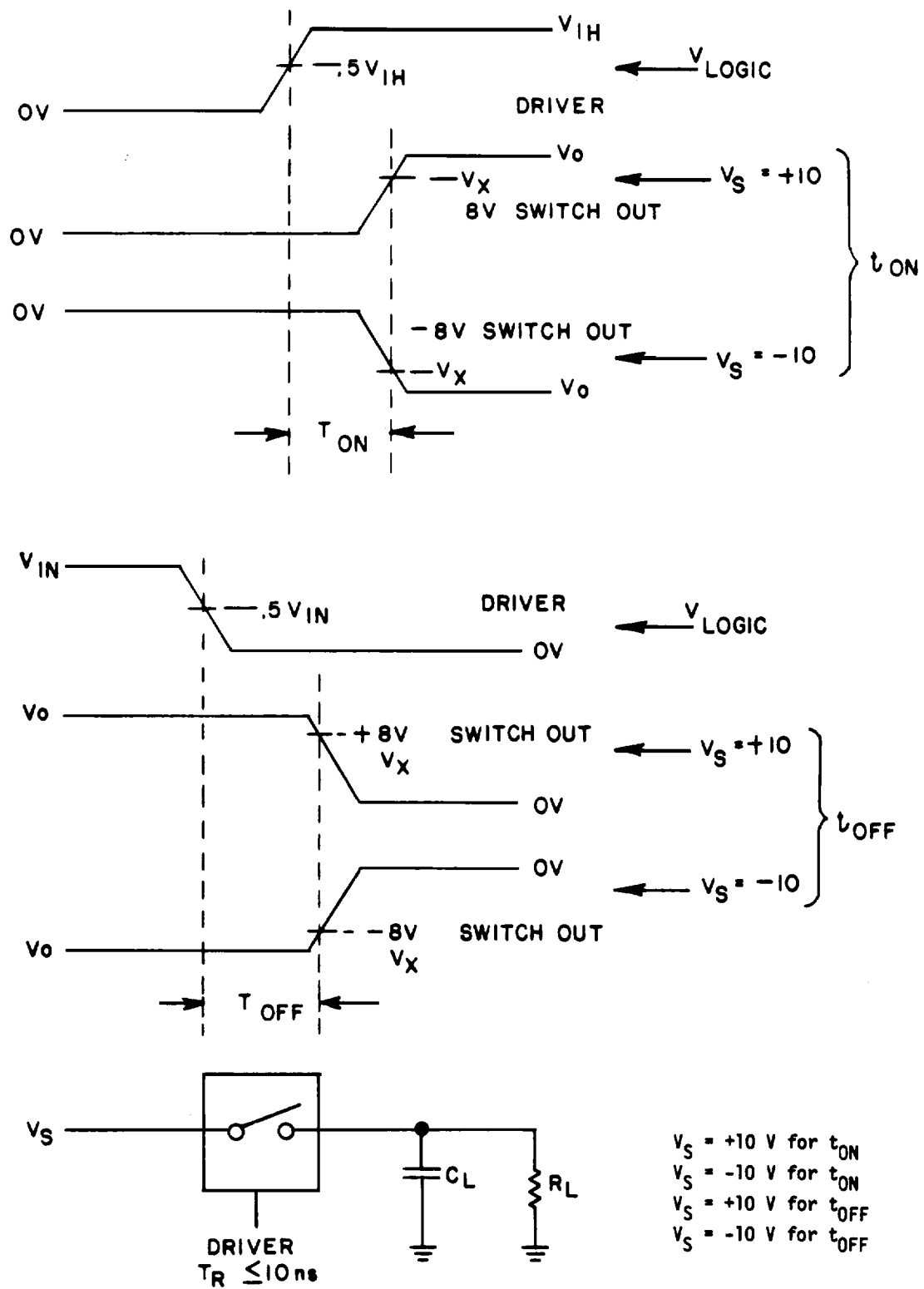
FIGURE 5.  $I_{D(off)}$  test circuit.



$I_I$  Test conditions are from table I.

FIGURE 7.  $I_{IL}, I_{IH}$  test circuit.

FIGURE 8.  $I^+, I^-$  test circuit.



$R_L = 1\text{ k}\Omega \pm 5\%$ .

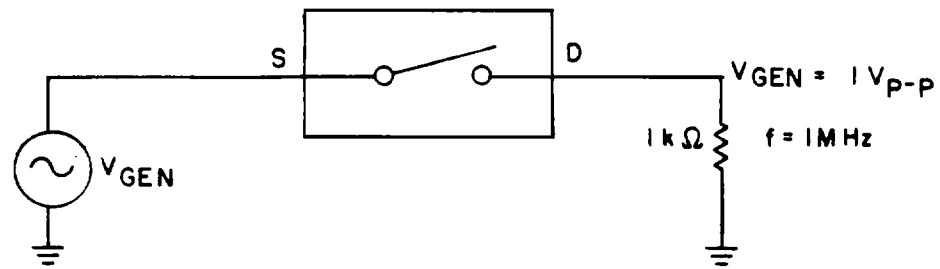
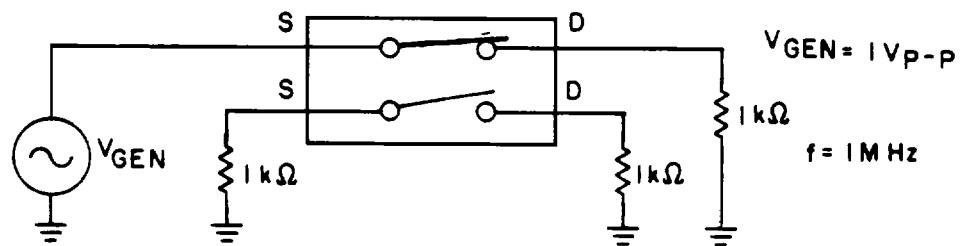
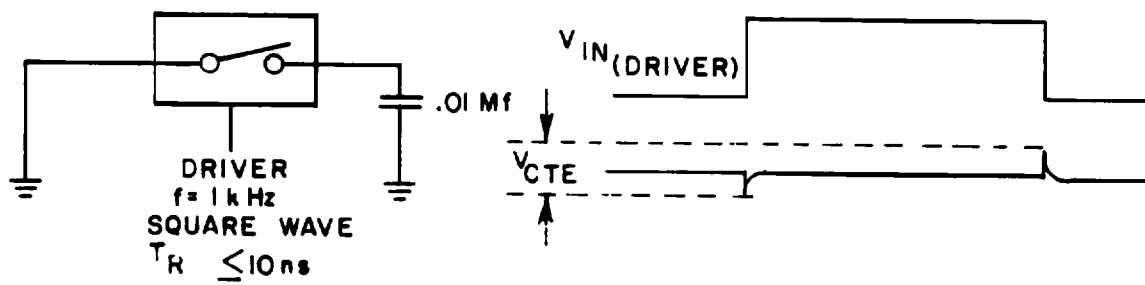
$C_L = 100\text{ pF} \pm 5\%$  (includes test and jig capacitance.)

FIGURE 9. Input-output waveforms for time delay tests.

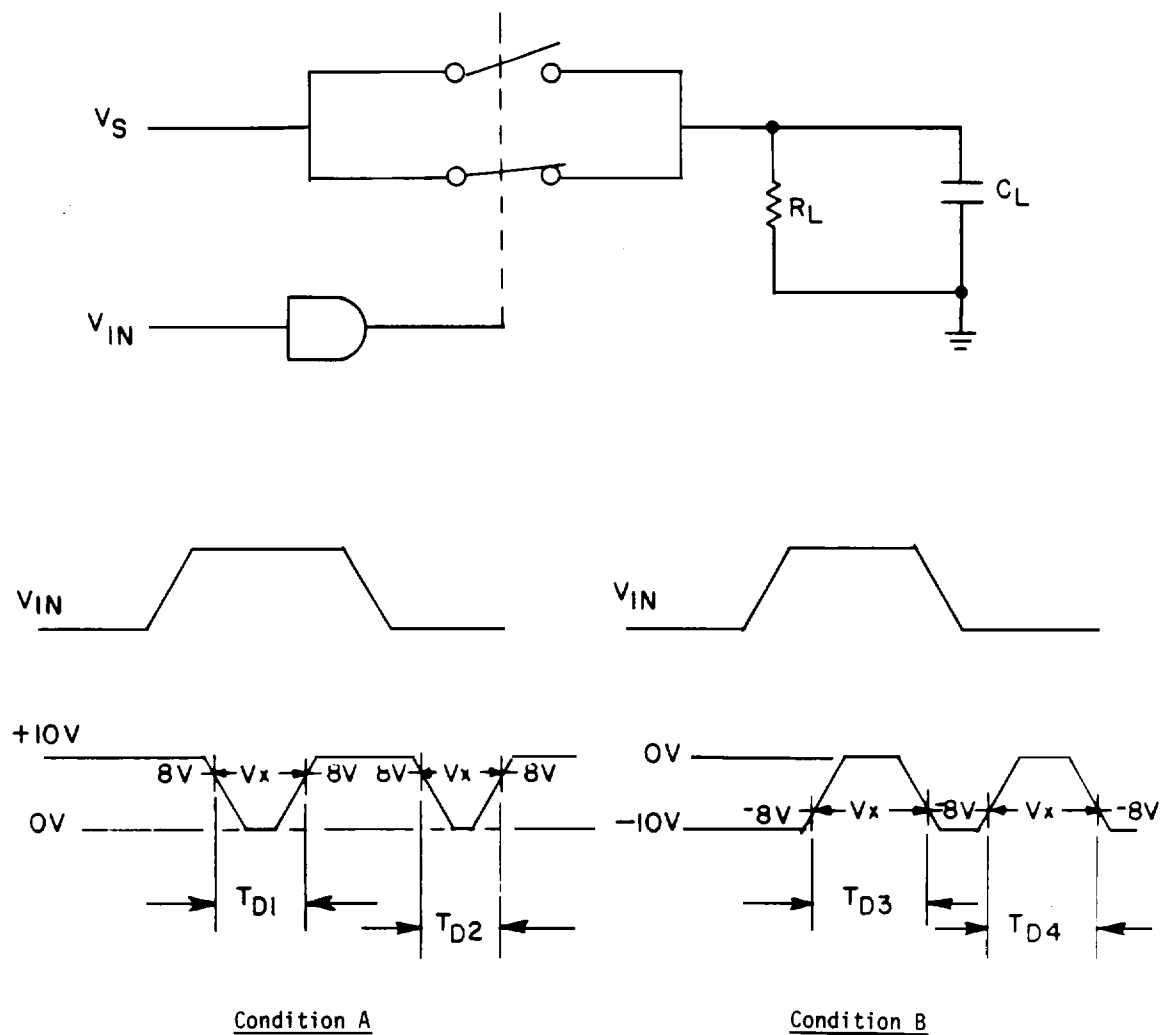
## NOTES:

1. The logic driver shall have the following characteristics:
  - a.  $V_{\text{LOGIC}} = 0 \text{ V to } +3 \text{ V}$  for device types 01 through 08.
  - b. Rise time (0.3 V to 2.7 V)  $\leq 10 \text{ ns}$  for device types 01 through 08.  
Fall time (2.7 V to 0.3 V)  $\leq 10 \text{ ns}$  for device types 01 through 08.
2. See 3.4.1 for appropriate switching conditions.
3.  $V_{\text{SOURCE}} (V_S) = +10 \text{ V}$  and  $-10 \text{ V}$  for  $t_{\text{ON}}$ .  
 $V_{\text{SOURCE}} (V_S) = +10 \text{ V}$  and  $-10 \text{ V}$  for  $t_{\text{OFF}}$ .
4.  $V_x = +8 \text{ V}$  for  $+10 \text{ V}$  condition in (3), above.  
 $V_x = -8 \text{ V}$  for  $-10 \text{ V}$  condition in (3), above.

FIGURE 9. Input-output waveforms for time delay tests - Continued.

FIGURE 10. Isolation test circuit.FIGURE 11. Crosstalk test circuit.FIGURE 12. Charge transfer error test circuit.





## NOTES:

1.  $R_L = 1 \text{ k}\Omega \pm 5\%$ ,  $C_L = 100 \text{ pF} \pm 5\%$ .
2.  $t_{D1}$ ,  $t_{D2}$ ,  $t_{D3}$ , and  $t_{D4}$  shall all be measured. These measurements shall apply only to device types 03, 04, and 07 (see 3.4.1 for switch conditions).
3.  $V_{\text{SOURCE}} (V_S) = +10 \text{ V}$  for condition A (all device types).  
 $V_{\text{SOURCE}} (V_S) = -10 \text{ V}$  for condition B (all device types).
4.  $V_x = +8 \text{ V}$  for condition A (all device types).  
 $V_x = -8 \text{ V}$  for condition B (all device types).
5. The logic driver shall have the following characteristics:
  - a.  $V_{\text{LOGIC}} = 0 \text{ V}$  to  $3 \text{ V}$  for device types 01 through 08.
  - b. Rise time ( $0.3 \text{ V}$  to  $2.7 \text{ V}$ )  $\leq 10 \text{ ns}$  for device types 01 through 08.  
 Fall time ( $2.7$  to  $0.3 \text{ V}$ )  $\leq 10 \text{ ns}$  for device types 01 through 08.

FIGURE 13. Break-before-make test circuit.

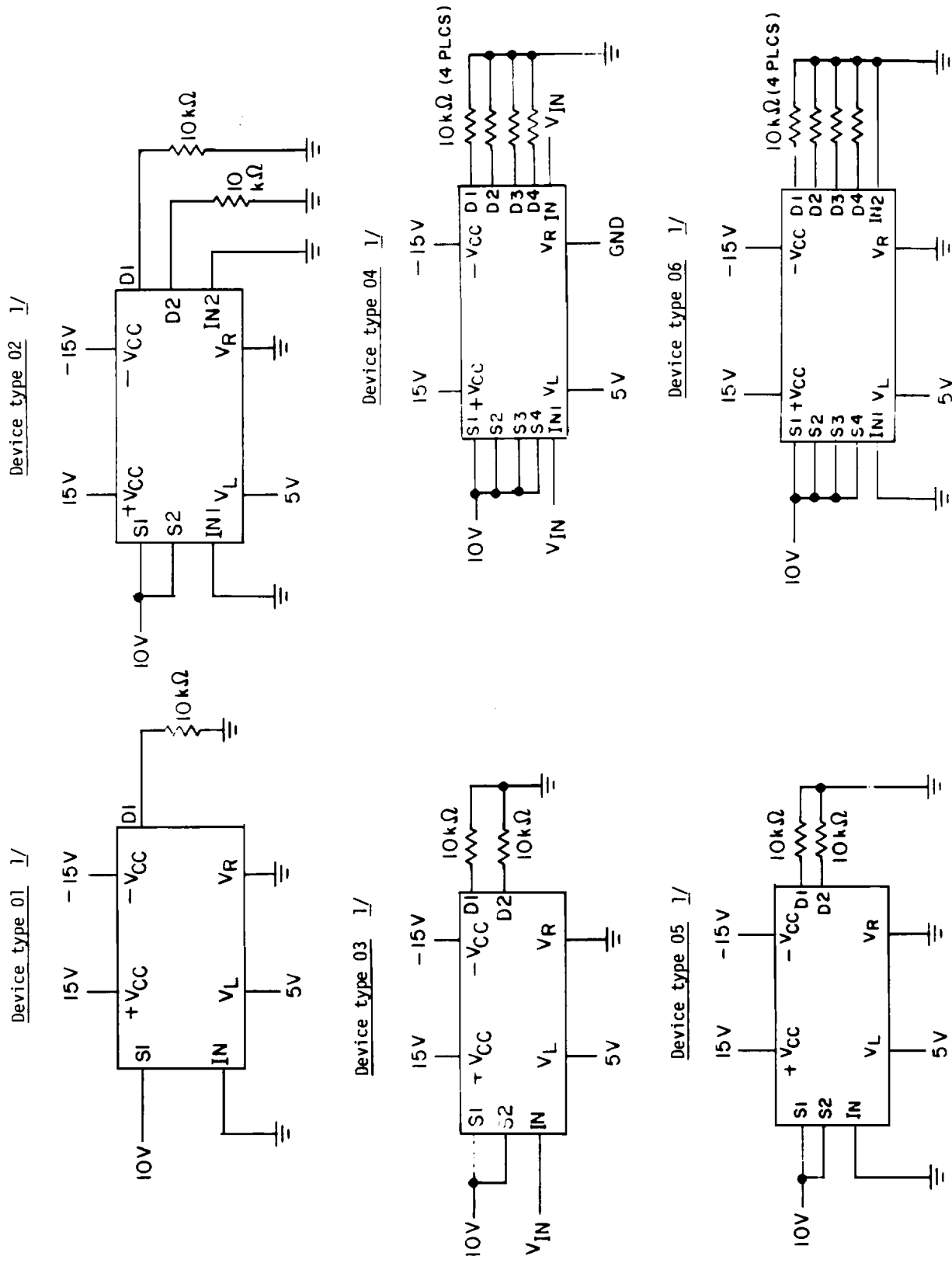
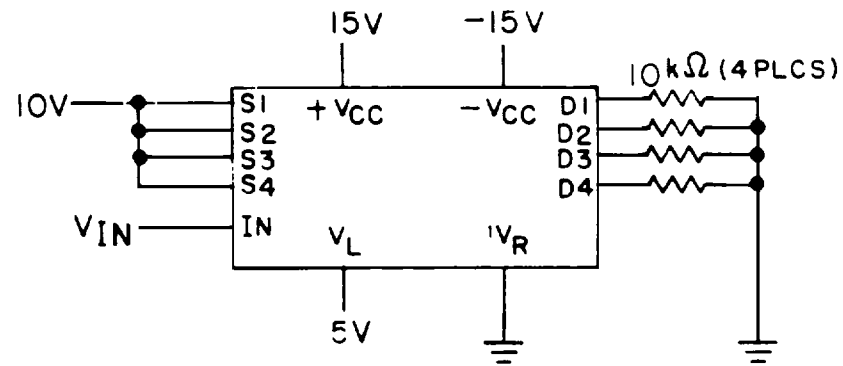
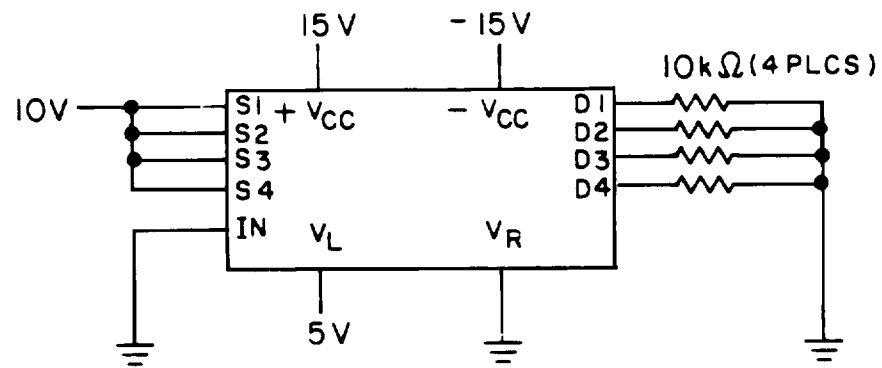


FIGURE 14. Test circuit, static burn-in and operating life test.

Device type 071/

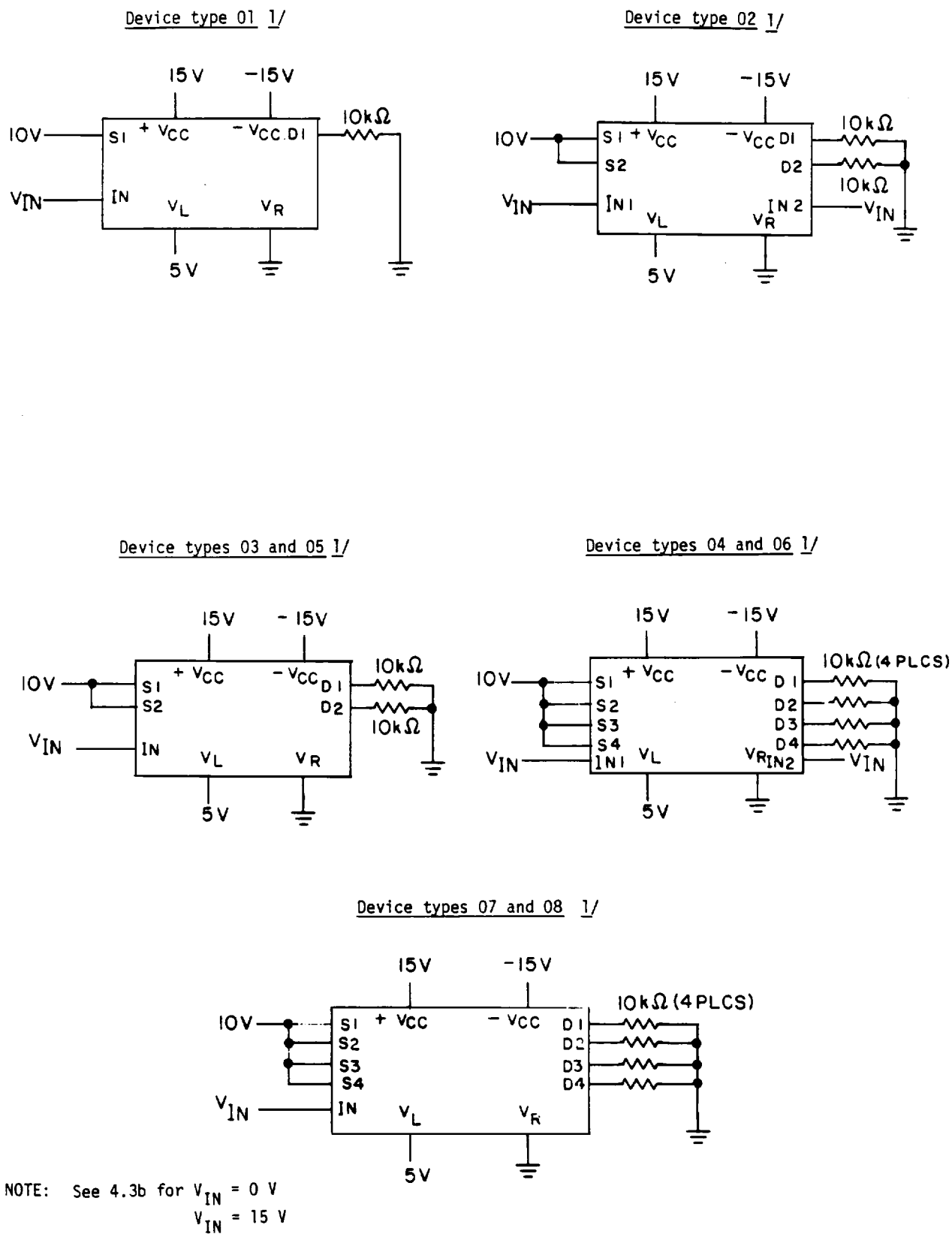


Device type 081/



NOTE: See 4.3b for  
 $V_{IN} = 0 \text{ V.}$   
 $V_{IN} = 15 \text{ V.}$

FIGURE 14. Test circuit, static burn-in and operating life test - Continued.

FIGURE 15. Test circuit, dynamic burn-in and operating life test.

NOTE: The pulse generator shall have the following characteristics:

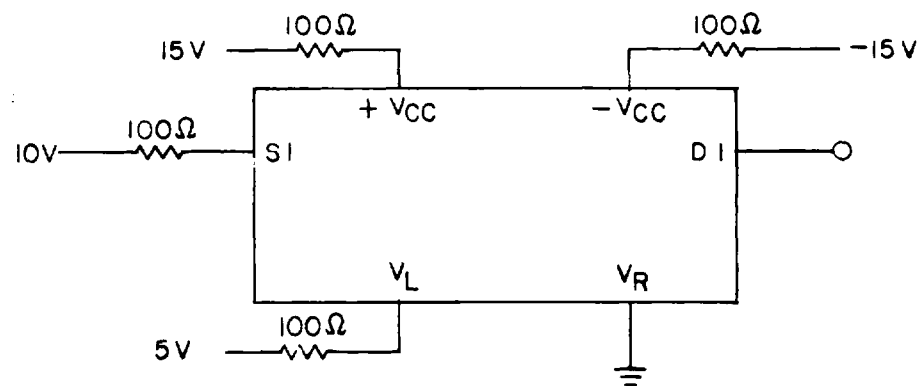
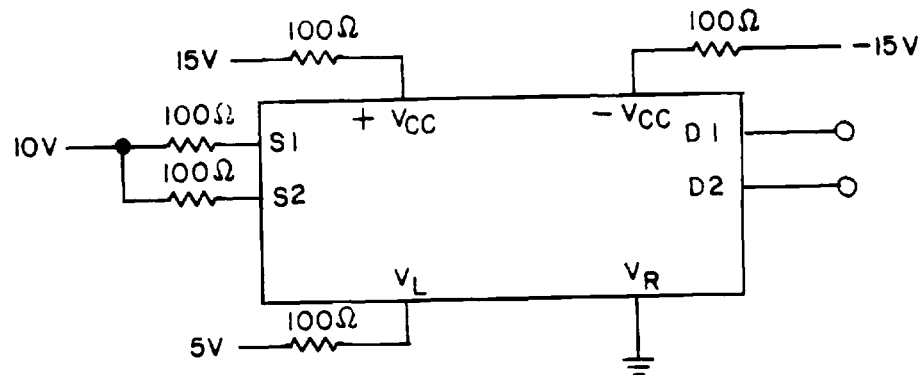
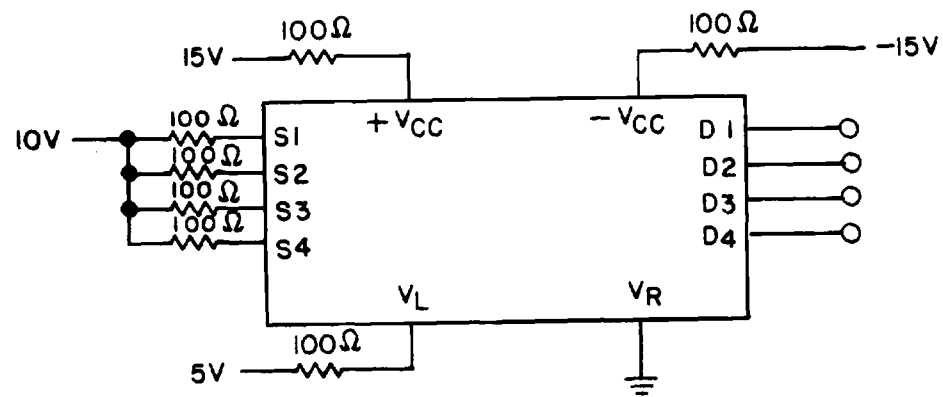
$V_{GEN} = 0 \text{ V to } 5 \text{ V.}$

Rise time  $\leq 10 \text{ ns.}$

Fall time  $\leq 10 \text{ ns.}$

PRR = 1 kHz at 50% duty cycle.

FIGURE 15. Test circuit, dynamic burn-in and operating life test - Continued.

Device type 01Device types 02, 03, and 05Device types 04, 06, 07, and 08FIGURE 16. Test circuit, accelerated burn-in and operating life test.

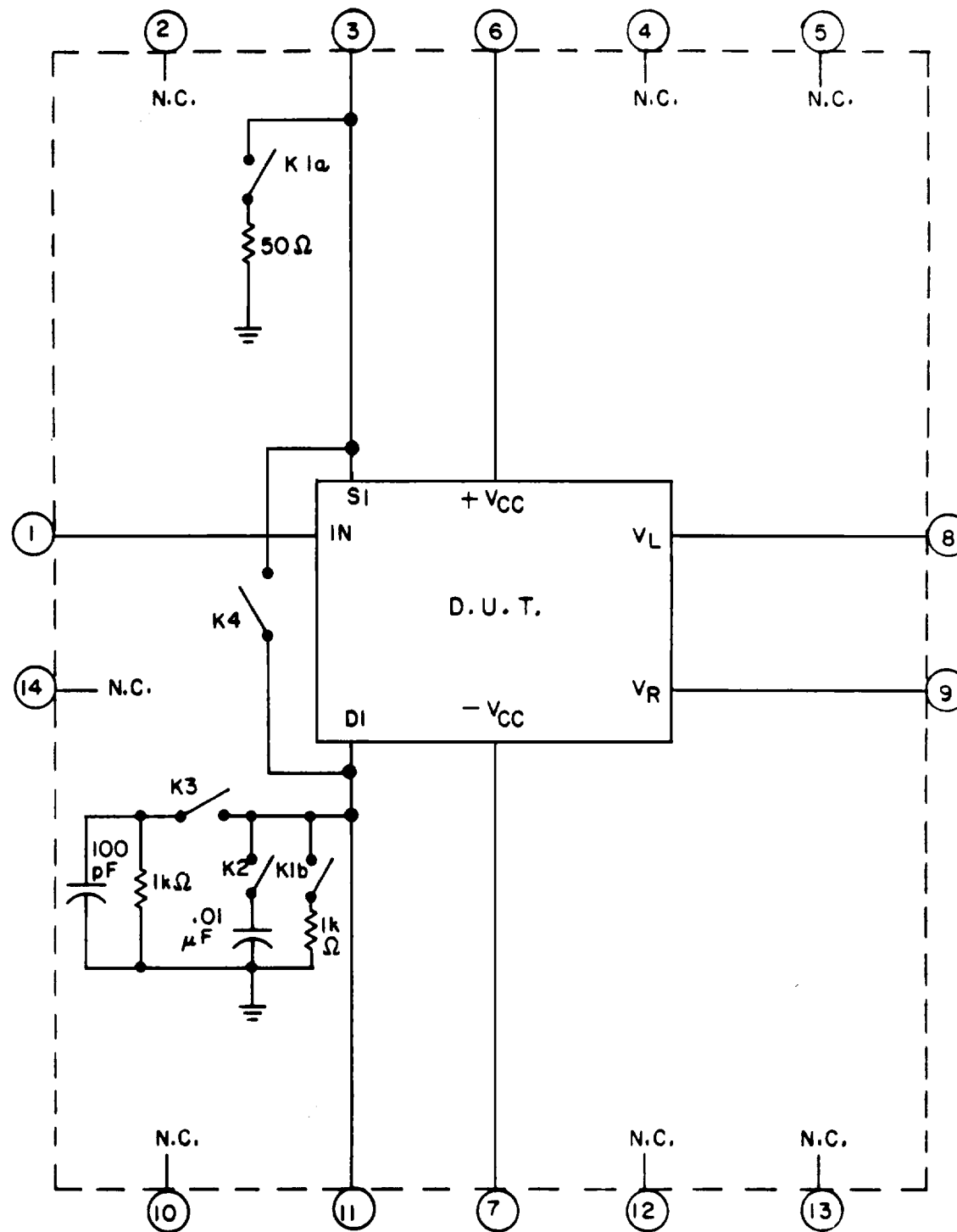


FIGURE 17. Test circuit (static and dynamic tests) for device type 01.

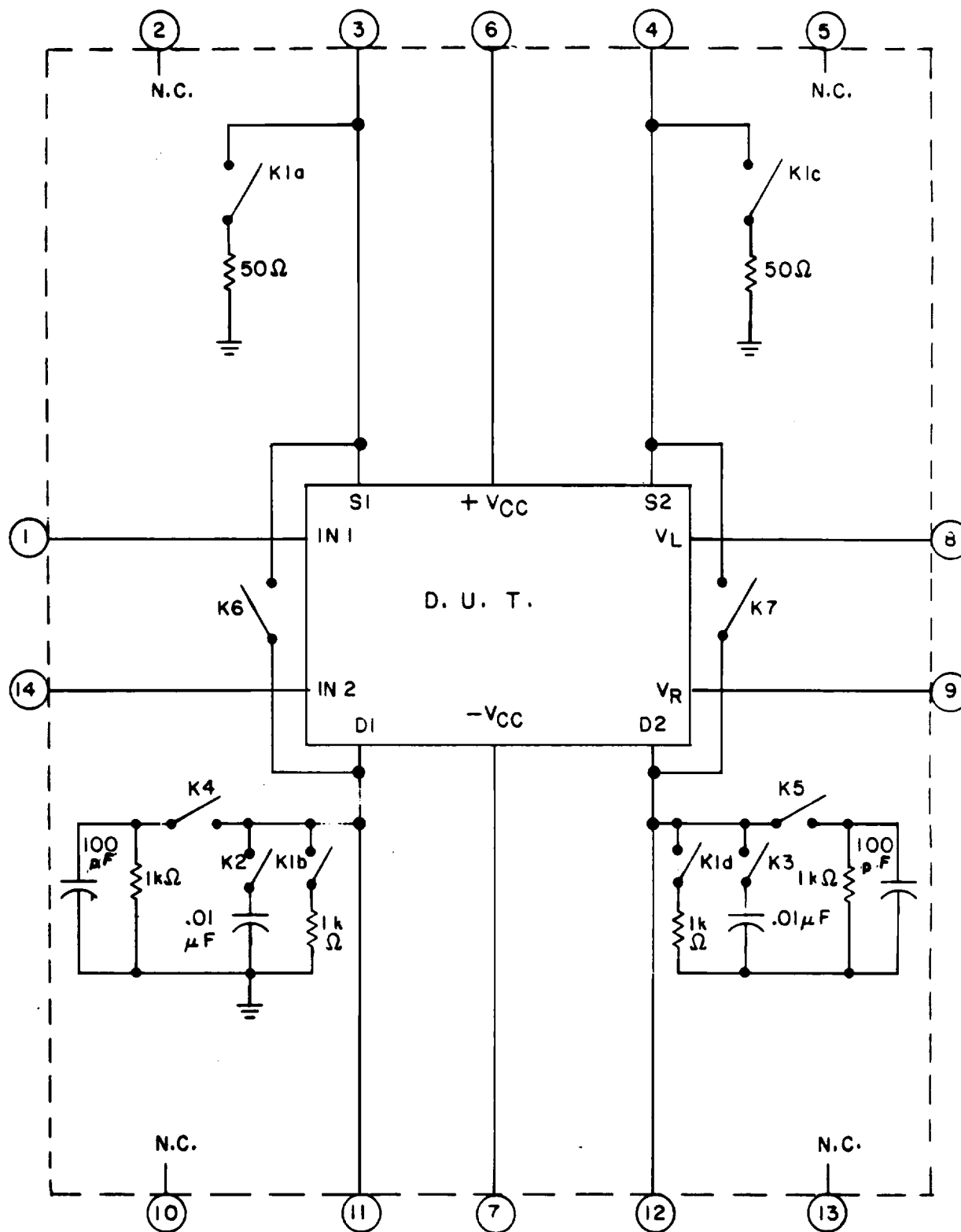


FIGURE 18. Test circuit (static and dynamic tests) for device type 02.



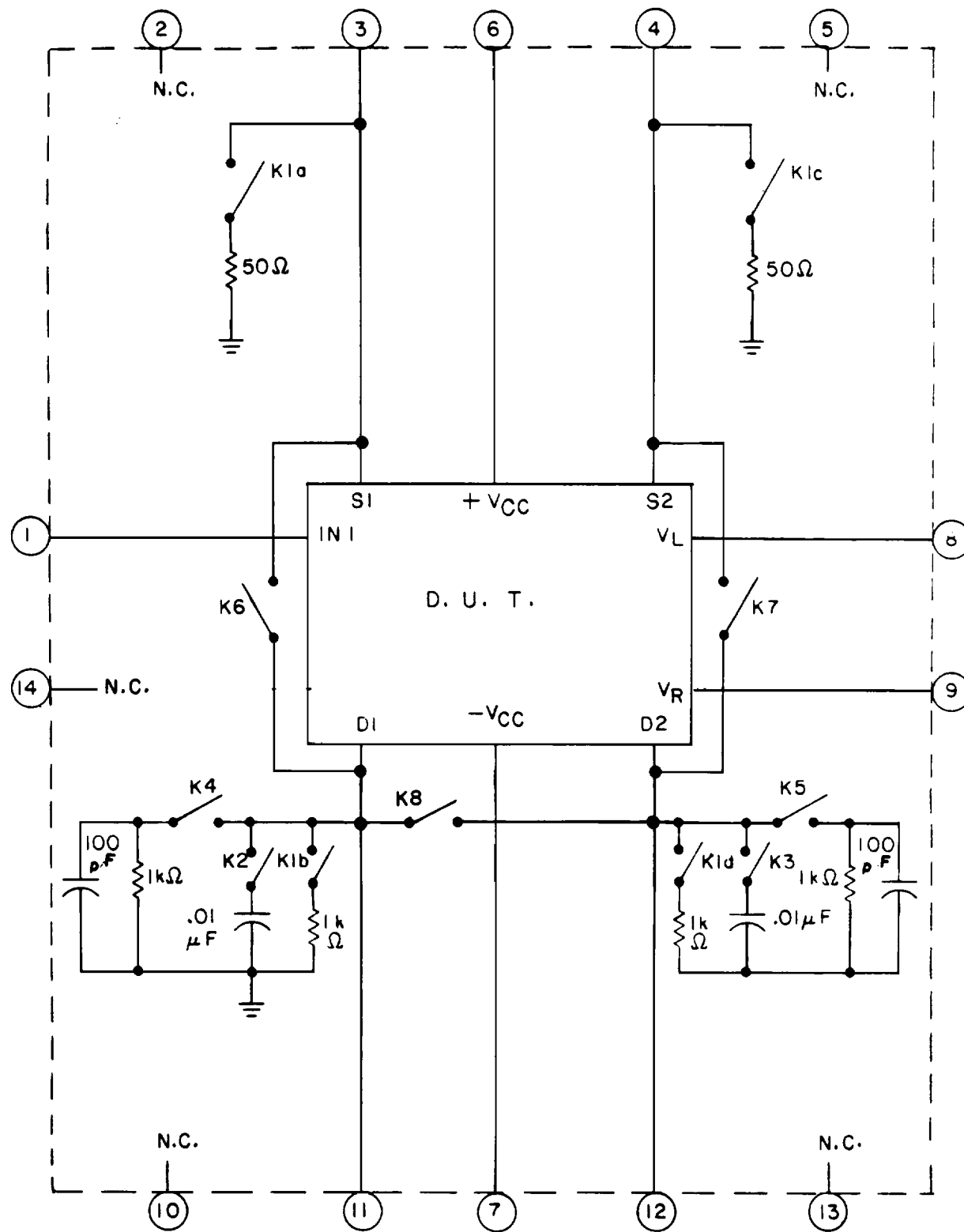


FIGURE 19. Test circuit (static and dynamic tests) for device types 03 and 05.

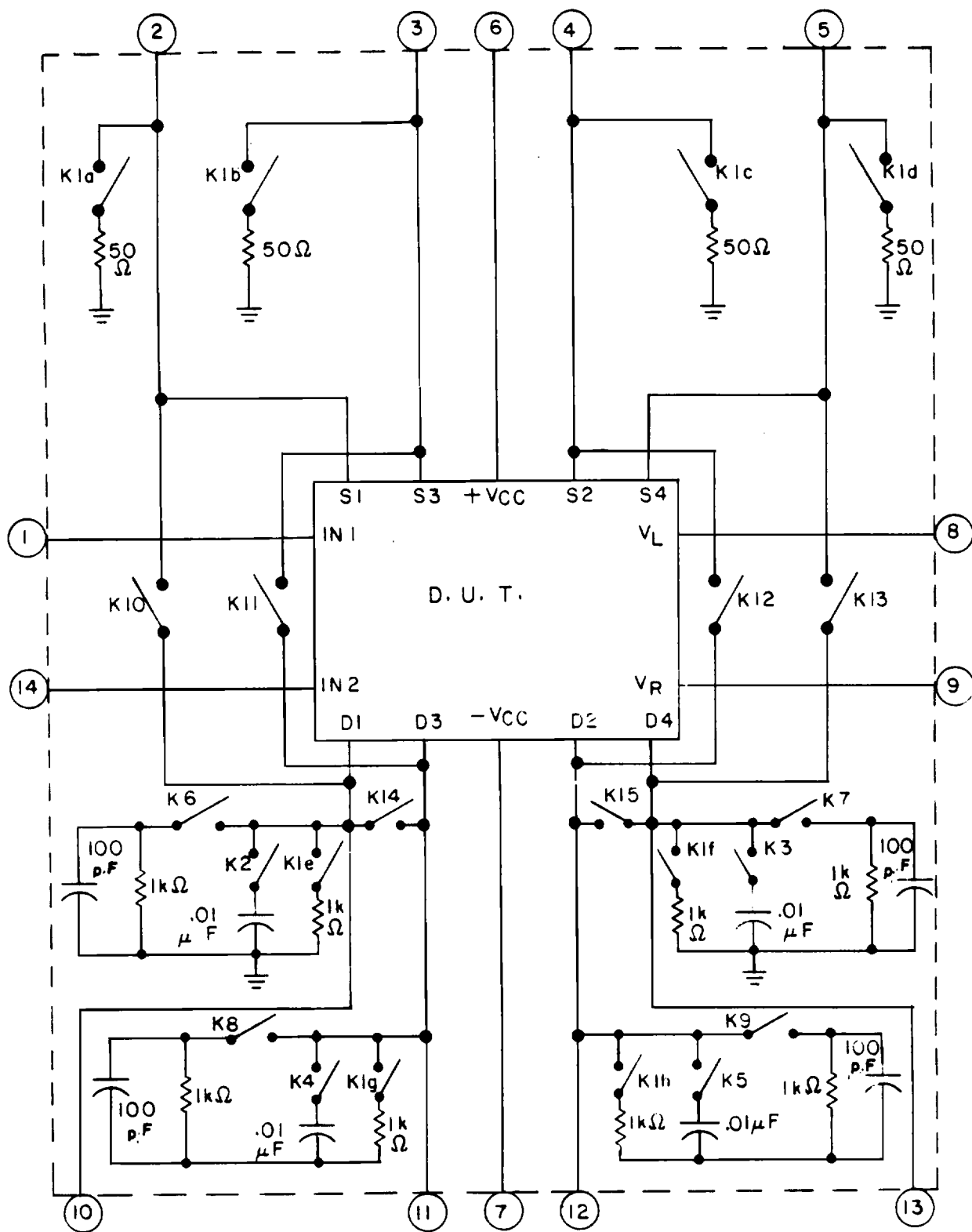


FIGURE 20. Test circuit (static and dynamic tests) for device types 04 and 06.

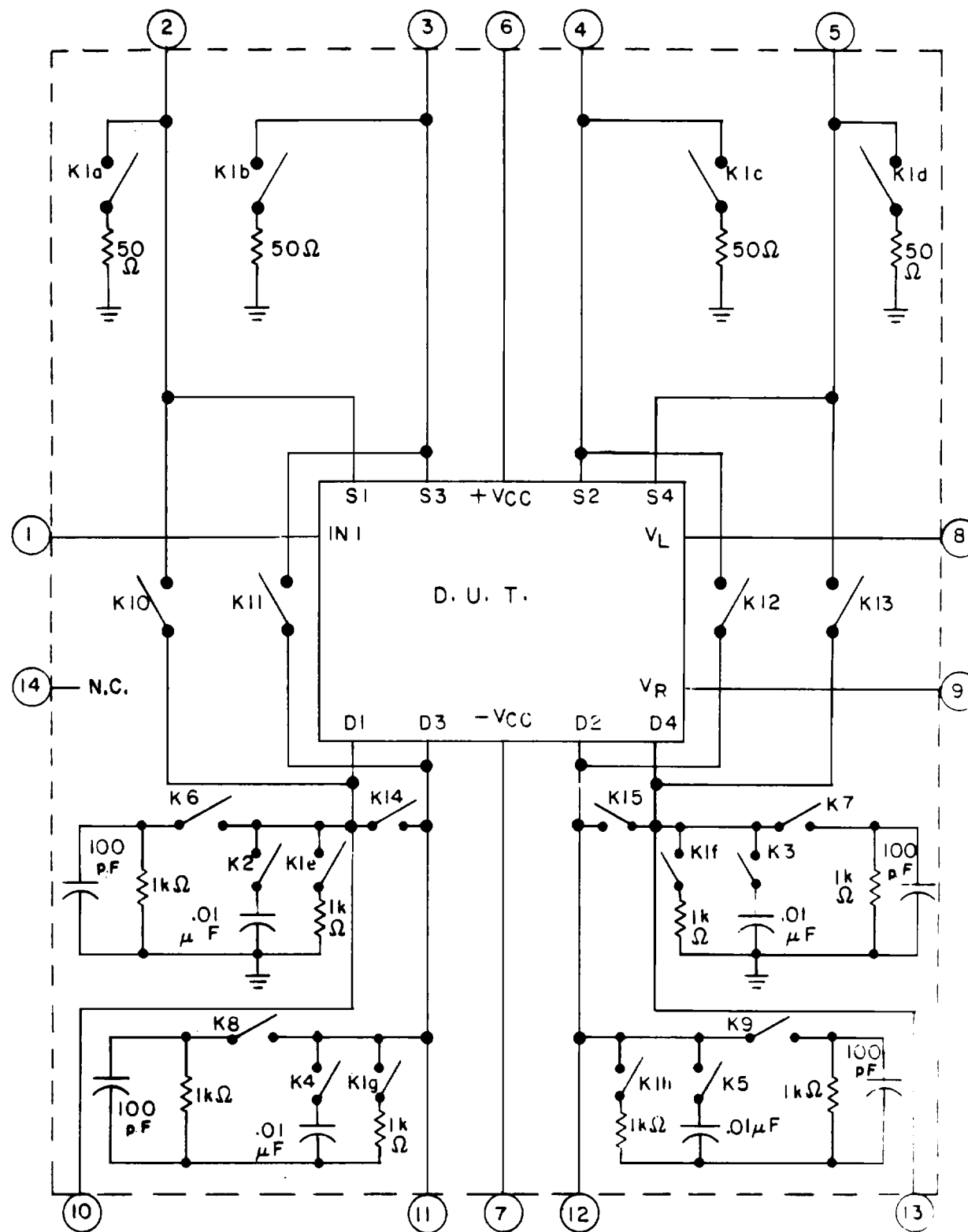


FIGURE 21. Test circuit (static and dynamic tests) for device types 07 and 08.





TABLE III. Group A inspection for device type 02 - Continued.

Symbol	Test number	Adapter pin number 1/												Test limits									
		IN1	M.C.	S1	S2	M.C.	+VCC	-VCC	V <sub>L</sub>	VR	M.C.	D1	D2	M.C.	IN2	Relays energized	Measured pin number	Subgroup 10 T.C. 25°C Min	Subgroup 10 T.C. 25°C Max	Subgroup 11 T.C. 25°C Min	Subgroup 11 T.C. 25°C Max	Unit	
EON	44	IN		IN			15.0 V	-15.0 V	+5.0 V	GND		OUT						1 to 11	---	550			ns
EON	45	IN		IN							OUT	OUT						14 to 12	---	550			
EOPF	46	IN		IN							OUT	OUT						1 to 11	---	400			
EON	48	IN		IN							OUT	OUT						14 to 12	---	400			
EON	49	IN		IN							OUT	OUT						1 to 11	---	375			
EON	50	IN		IN							OUT	OUT						14 to 12	---	375			
EOPF	51	IN		IN							OUT	OUT						1 to 11	---	190			
ICA	52	10.0 V																14 to 12	---	190			
	53													10.0 V	None		14						pf
CTS	54																3						
	55																4						
ICDs	56																11						
	57																12						

See notes at end of table.

TABLE III. Group A Inspection for device type 03, 05.

Symbol	Test number	Adapter pin number 1/															Test limits						
		1	2	3	4	5	6	7	8	9	10	11	12	13	14	Relays energized	Measured pin number	Subgroup 1 T <sub>c</sub> = 25°C Min	Subgroup 1 T <sub>c</sub> = 25°C Max	Subgroup 2 T <sub>c</sub> = 125°C Min	Subgroup 2 T <sub>c</sub> = 125°C Max	Subgroup 3 T <sub>c</sub> = -55°C Min	Subgroup 3 T <sub>c</sub> = -55°C Max
IBB	1	0.0 V	2.4 V													None	3	19.25	-9.25	-8.50	-8.25	19.25	-9.25
	2	2.4 V		10.0 mA	10.0 mA											None	4	19.25	-9.25	-8.50	-8.25	19.25	-9.25
	3	0.0 V		-10.0 mA	-10.0 mA											None	3	19.25	-9.25	-8.50	-8.25	19.25	-9.25
	4	2.4 V		10.0 mA	10.0 mA											None	4	19.25	-9.25	-8.50	-8.25	19.25	-9.25
	5	2.4 V		10.0 mA	10.0 mA											None	4	19.25	-9.25	-8.50	-8.25	19.25	-9.25
	6	2.4 V		10.0 mA	10.0 mA											None	4	19.25	-9.25	-8.50	-8.25	19.25	-9.25
	7	0.0 V		-10.0 mA	-10.0 mA											None	4	19.25	-9.25	-8.50	-8.25	19.25	-9.25
	8	2.4 V		-10.0 mA	-10.0 mA											None	3	16.75	-6.75	6.0	6.75	16.75	-6.75
IB(OFF)	9	0.0 V		10.0 V	10.0 V											K7	4	-2	2	-200	200	-200	200
	10	0.0 V		10.0 V	10.0 V											K6	3						
	11	0.0 V		-10.0 V	-10.0 V											K7	3						
IB(OFF)	12	2.4 V		10.0 V	10.0 V											None	11	-1	1	-100	100	-100	100
	13	0.0 V		-10.0 V	-10.0 V											None	12						
	14	2.4 V		10.0 V	10.0 V											None	11						
	15	2.4 V		10.0 V	10.0 V											None	11						
IB(OFF)	16	2.4 V		10.0 V	10.0 V											None	12						
	17	0.0 V		-10.0 V	-10.0 V											None	3						
	18	2.4 V		10.0 V	10.0 V											None	3						
	19	0.0 V		-10.0 V	-10.0 V											None	3						
IBL	20	2.4 V		10.0 V	10.0 V											None	4	-1	0	-10	0	-1	0
	21	0.0 V		10.0 V	10.0 V											None	1	-1	0	-10	0	-1	0
IIN	22	2.4 V	2.4 V														1	0	1	0	10	0	1
	23	5.0 V	5.0 V														1	0	1	0	10	0	1
+ICC	24	0.0 V	0.0 V														6	---	10	---	100	---	10
	25	5.0 V	5.0 V														6	---	10	---	100	---	10
	26	0.0 V	0.0 V														7	-10	---	-100	---	-10	---
-ICC	27	5.0 V	5.0 V														7	-10	---	-100	---	-10	---
	28	0.0 V	0.0 V														8	---	10	---	100	---	10
+IL	29	5.0 V	5.0 V														8	---	10	---	100	---	10
	30	5.0 V	5.0 V														9	-10	---	-100	---	-10	---
-IL	31	5.0 V	5.0 V														9	-10	---	-100	---	-10	---
	31	5.0 V	5.0 V														9	-10	---	-100	---	-10	---

See notes at end of table.







TABLE III. Group A inspection for device type 05, 06 - Continued.

Symbol	Test number	Adapter pin number 1/											Measured pin number	Test limits		Unit		
		S1	S2	S3	S4	+VCC	-VCC	V <sub>L</sub>	V <sub>H</sub>	D1	D2	D3		D4	IM2		Min	Max
		1	2	3	4	5	6	7	8	9	10	11		12	13			
V <sub>CR</sub>	55 56 57 58	IN 2/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	IN 3/	10	15		dB
V <sub>CT</sub>	59 60	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	12 10	3.16 3.16		dB
V <sub>ISO</sub>	61 62 63 64	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	10 11 12 13	3.16 50		dB
V <sub>OH</sub>	65 66 67 68	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	OUT	OUT	OUT	OUT	IN 2/	2 to 10 3 to 12 4 to 12 5 to 13	1450		dB
V <sub>OFF</sub>	69 70 71 72	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	OUT	OUT	OUT	OUT	IN 2/	2 to 10 3 to 11 4 to 12 5 to 13	1250		dB
V <sub>OH</sub>	73 74 75 76	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	OUT	OUT	OUT	OUT	IN 2/	2 to 10 3 to 11 4 to 12 5 to 13	1550		dB
V <sub>OFF</sub>	77 78 79 80	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	OUT	OUT	OUT	OUT	IN 2/	2 to 10 3 to 11 4 to 12 5 to 13	1400		dB
V <sub>OH</sub>	81 82 83 84	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	OUT	OUT	OUT	OUT	IN 2/	2 to 10 3 to 11 4 to 12 5 to 13	375		dB
V <sub>OFF</sub>	85 86 87 88	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	OUT	OUT	OUT	OUT	IN 2/	2 to 10 3 to 11 4 to 12 5 to 13	190		dB
V <sub>A</sub>	89 90	0.0 V	0.0 V	0.0 V	0.0 V	0.0 V	0.0 V	0.0 V	0.0 V	None	None	None	None	None	1 14	6 6		dB
V <sub>IS</sub>	91 92 93 94														2 3 4 5	10		
V <sub>OS</sub>	95 96 97 98 99														10 11 12 13			
V <sub>D</sub> 2/	100 101 102	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	IN 2/	10 11 12 13	20		dB

See notes at end of Table.

TABLE III. Group A inspection for device type 08, 06 - Continued.

Symbol	Test number	Aapter pin number I/													Relays energized	Measured pin number	Test limits			Unit	
		1	2	3	4	5	6	7	8	9	10	11	12	13			14	Subgroup 1A TC = 125°C	Subgroup 1A TC = -55°C		Min
T <sub>D</sub> 2/	103	IN	IN	IN	IN	IN	-15.0 V	+5.0 V	GND	IN	IN	IN	IN	IN	IN	20	---	---	---	---	ps
	104	IN	IN	IN	IN	IN	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	
	105	IN	IN	IN	IN	IN	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	
T <sub>D</sub> 3/	106	IN	IN	IN	IN	IN	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	ps
	107	IN	IN	IN	IN	IN	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	
	108	IN	IN	IN	IN	IN	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	
	109	IN	IN	IN	IN	IN	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	ps
	110	IN	IN	IN	IN	IN	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	↑	

See notes at end of table.



TABLE III. Group A inspection for device type DT, DB - Continued.

Symbol	Test number	Adapter pin number 1/															Measures number	Test limits				Unit	
		1	2	3	4	5	6	7	8	9	10	11	12	13	14	15		Subgroup 8		Min	Max		Unit
																		T <sub>C</sub> = 25°C	T <sub>C</sub> = 25°C				
ECTE	52	↑					↑										↑	10			↑	no	
	53						↑										↑	11			↑	no	
	54						↑										↑	12			↑	no	
	55						↑										↑	13			↑	no	
ECT	56	↑				↑			GND								↑	12			↑	no	
	57	↑				↑			GND								↑	10			↑	no	
	58	↑				↑			GND								↑	10			↑	no	
	59	↑				↑			GND								↑	11			↑	no	
	60	↑				↑			GND								↑	12			↑	no	
	61	↑				↑			GND								↑	13			↑	no	
TON	62	↑				↑			GND								↑	10			↑	no	
	63	↑				↑			GND								↑	11			↑	no	
	64	↑				↑			GND								↑	12			↑	no	
	65	↑				↑			GND								↑	13			↑	no	
	66	↑				↑			GND								↑	10			↑	no	
TOFF	67	↑				↑			GND								↑	10			↑	no	
	68	↑				↑			GND								↑	11			↑	no	
	69	↑				↑			GND								↑	12			↑	no	
	70	↑				↑			GND								↑	10			↑	no	
	71	↑				↑			GND								↑	11			↑	no	
LOFF	72	↑				↑			GND								↑	10			↑	no	
	73	↑				↑			GND								↑	11			↑	no	
	74	↑				↑			GND								↑	10			↑	no	
	75	↑				↑			GND								↑	11			↑	no	
	76	↑				↑			GND								↑	12			↑	no	
	77	↑				↑			GND								↑	13			↑	no	
	78	↑				↑			GND								↑	10			↑	no	
CA	79	↑				↑			GND								↑	2 to 10			↑	no	
	80	↑				↑			GND								↑	3 to 11			↑	no	
	81	↑				↑			GND								↑	4 to 12			↑	no	
	82	↑				↑			GND								↑	5 to 13			↑	no	
	83	↑				↑			GND								↑	2 to 10			↑	no	
CIS	84	↑				↑			GND								↑	3 to 11			↑	no	
	85	↑				↑			GND								↑	4 to 12			↑	no	
	86	↑				↑			GND								↑	5 to 13			↑	no	
	87	↑				↑			GND								↑	2 to 10			↑	no	
	88	↑				↑			GND								↑	3 to 11			↑	no	
COS	89	↑				↑			GND								↑	4 to 12			↑	no	
	90	↑				↑			GND								↑	5 to 13			↑	no	
	91	↑				↑			GND								↑	1			↑	no	
	92	↑				↑			GND								↑	2			↑	no	
	93	↑				↑			GND								↑	3			↑	no	
TD 5/	94	↑				↑			GND								↑	4			↑	no	
	95	↑				↑			GND								↑	5			↑	no	
	96	↑				↑			GND								↑	10			↑	no	
	97	↑				↑			GND								↑	11			↑	no	
	98	↑				↑			GND								↑	12			↑	no	

See notes at end of table

TABLE III. Group A inspection for device type 01, 06 - Continued.

Symbol	Test number	Adapter pin number														Measured pin number	Subgroup 1A TC = 125°C		Subgroup 1B TC = 55°C	Unit		
		1A	2	3	4	5	6	7	8	9	10	11	12	13	14		15	16			17	18
V <sub>D</sub> Z/	99	IM	IM	IM															20			
	100	IM	IM	IM	IM		15.0 V	-15.0 V	+5.0 V	GND												
	101	IM	IM	IM	IM	IM																
V <sub>D</sub> Z/	102																					
	103	IM	IM	IM	IM																	
	104	IM	IM	IM	IM	IM																
	105																					
	106																					

## NOTES:

- The test circuits used with table III are shown in figures 17, 18, 19, 20 and 21. The waveforms of figure 9 apply to all device types as specified in table III (see tests for 08 and 09). The waveforms of figure 13 apply to devices 03, 04, and 07 only as specified.
- Responses may be measured differentially with respect to V<sub>A</sub>. In case of differentially measured voltages, the table III limits representing voltage drop across the tested switch must be maintained.
- The input pulse generator shall have the following characteristics: V<sub>GH</sub> = 0-3V for all device types; rise time/fall time  $\leq 10$  ns;  $P_{DR} = 1$  MS @ 50 percent duty cycle.
- The input generator shall have the following characteristics: V<sub>GH</sub> = 1 VP-P at 1 MS.
- Break-before-make test applies to devices 03, 04, and 07 only.
- Conditions for device type 05 only.
- Conditions for device type 06 only.
- Conditions for device type 08 only.
- Conditions for device type 08 only.
- Conditions for device type 07 only.

4.4.1 Group A inspection. Group A inspection shall be in accordance with table I of method 5005 of MIL-STD-883 and as follows:

- a. Subgroups 5, 6, and 8 shall be omitted.
- b. Tests shall be as specified in table II.
- c. Special subgroups shall be added to group A inspection and shall consist of group A subgroups 12, 13, and 14 as specified in table III herein. The LTPD for subgroup 12 shall be 5 for all classes; the LTPD for subgroup 13 shall be 5 for all classes; the LTPD for subgroup 14 shall be 5 for all classes.
- d.  $C_x$  measurements shall be made only for initial qualification and after process or design changes which may effect capacitance measurements. Capacitance shall be measured between the designated terminal and ground at a frequency of 1 MHz (see method 3012.1 of MIL-STD-883).  $C_{IS}$  and  $C_{OS}$  tests shall be measured with the switch off (see 3.4.1).

4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of method 5005 of MIL-STD-883 and as follows:

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Life test for class S shall be performed as specified in subgroup 5 of table IIa of method 5005 of MIL-STD-883 using the circuit shown on figure 16. If the alternate burn-in conditions are used, the circuit shown on figure 15 shall be used.
- c. A special subgroup shall be added using an LTPD of 15 for all classes. This subgroup shall consist of a high voltage test of the input protection circuits,  $V_{ZAp}$  (see 4.5.3).

4.4.3 Group C inspection. Group C inspection shall be in accordance with table III of method 5005 of MIL-STD-883 and as follows:

- a. End-point electrical parameters shall be as specified in table IV. Delta limits shall apply only to subgroup I of group C inspection for classes B and C devices.
- b. Life tests for classes B and C (method 1005 of MIL-STD-883): Test condition C using the circuit shown on figure 15, or test condition D using the circuit shown on figure 14, or test condition F using the circuit shown on figure 16.

4.4.4 Group D inspection. Group D inspection shall be in accordance with table IV of method 5005 of MIL-STD-883 and as follows:

- a. End-point electrical parameters shall be as specified in table II herein.
- b. A special subgroup shall be added to group D inspection and it shall consist of the group A subgroups 4 and 7 as specified in table III herein.
- c. During the initial qualification, subgroup 6 shall be performed on one device for each device type to be qualified from those listed in 1.2.1 herein. After initial qualification, subgroup 6 shall be performed periodically on a single device selected from the device types previously qualified. When more than one device type was initially qualified, the single device selected shall be a different device type for each subsequent periodic inspection until all qualified device types have been inspected. The sequence of single device types shall be repeated to fulfill the periodic inspection requirement.

TABLE IV. Group C end-point electrical parameters.  
( $T_c = 25^\circ\text{C}$ ,  $\pm V_{CC} = \pm 15\text{ V}$ )

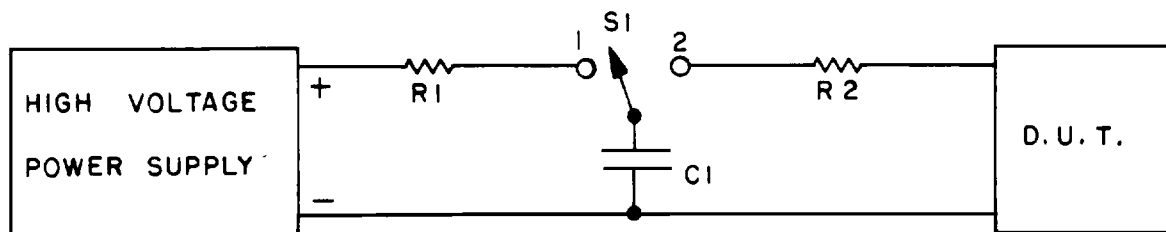
Test	Device types 01 - 08		
	Limits		Delta
	Minimum	Maximum	
$R_{DS}$	9.25 V	10.00 V	50 mV
$R_{DS}$	-10.00 V	-9.25 V	50 mV
$I_{S(OFF)}$	-1 nA	1 nA	$\pm 0.5\text{ nA}$
$I_{D(OFF)}$	-1 nA	1 nA	$\pm 0.5\text{ nA}$

4.5 Methods of inspection Methods of inspection shall be as specified in the appropriate tables. Electrical test circuits as prescribed herein or in the referenced test methods of MIL-STD-883 shall be acceptable. Other test circuits shall require the approval of the qualifying activity.

4.5.1 Voltage and current. All voltage values given, except differential voltages, are referenced to the external zero reference level of the supply voltage. Currents given are conventional current and positive when flowing into the referenced terminal.

4.5.2 Life test cooldown procedure. When devices are measured at 25°C following application of the operating life or burn-in test condition, they shall be cooled to room temperature prior to removal of the bias.

4.5.3 High voltage ( $V_{ZAP}$ ) test of input protection circuits. Unless otherwise specified, all input terminals of the device under test (DUT) shall be subjected to a voltage pulse from a high voltage source. This destructive test shall be conducted as follows using the test circuit shown below.



$V_{ZAP} = 400$  V charge on C1.  
 $10 \text{ M}\Omega \leq R1 \leq 50 \text{ M}\Omega$ .  
 $R2 = 1.5 \text{ k}\Omega$ .  
 $C1 = 100 \text{ pF}$ .  
 $S1 = \text{Hg-wetted "bounceless" relay}$ .

- a. Measure  $I_{IL}$  and  $I_{IH}$  at the inputs selected at 25°C. The test limit for each input tested shall be +1  $\mu\text{A}$  for  $I_{IH}$  and -1  $\mu\text{A}$  for  $I_{IL}$  at  $V(\text{supply}) = \pm 15$  V.
- b.  $V_{ZAP}$  is applied to the DUT in the following two modes (see table V) by charging C1 to  $V_{ZAP}$  with S1 in position 1 and then switching to position 2.

TABLE V. Modes for high voltage testing.

Mode	+ Terminal	- Terminal
1	+ VCC	Input
2	Input	- VCC

- c. Within 24 hours, repeat  $I_{IL}$  and  $I_{IH}$  measurements (see a. above) in accordance with table III. If a DUT exhibits values in excess of the specified limits after the  $V_{ZAP}$  test, it shall be classified as a failure.

## 5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.

## 6. NOTES

6.1 Notes. The notes specified in MIL-M-38510 are applicable to this specification.



6.2 Intended use. Microcircuits conforming to this specification are intended for use for Government microcircuit applications (original equipment) and logistic purposes.

6.3 Ordering data. Procurement documents should specify the following:

- a. Complete part number (see 1.2).
- b. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
- c. Requirement for certificate of compliance, if applicable.
- d. Requirements for notification of change of product or process to procuring activity in addition to notification to the qualifying activity, if applicable.
- e. Requirements for failure analysis (including required test condition of method 5003), corrective action and reporting of results, if applicable.
- f. Requirements for quality assurance options.
- g. Requirements for carriers, special lead lengths or lead forming, if applicable. These requirements shall not affect the part number. Unless otherwise specified, these requirements shall not apply to direct purchase by or direct shipment to the Government.

6.4 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-STD-1331, MIL-M-38510, and as follows:

+VCC	- - - - -	Positive supply voltage.
-VCC	- - - - -	Negative supply voltage.
+ICC	- - - - -	Positive supply current.
-ICC	- - - - -	Negative supply current.
V <sub>L</sub>	- - - - -	Logic supply voltage.
I <sub>L</sub>	- - - - -	Logic supply current.
R <sub>DS</sub>	- - - - -	Resistance of an "ON" switch.
V <sub>D</sub>	- - - - -	Drain voltage.
V <sub>S</sub>	- - - - -	Source voltage.
I <sub>D(ON)</sub>	- - - - -	Leakage current from an "ON" driver into the switch.
I <sub>D(OFF)</sub>	- - - - -	Leakage current into the drain terminal of an "OFF" switch.
I <sub>S(OFF)</sub>	- - - - -	Leakage current into the source terminal of an "OFF" switch.
t <sub>ON</sub>	- - - - -	Switching time as defined on figure 9.
t <sub>OFF</sub>	- - - - -	Switching time as defined on figure 9.
V <sub>CTE</sub>	- - - - -	Charge transfer error.
V <sub>CT</sub>	- - - - -	Crosstalk between switches.
V <sub>ISO</sub>	- - - - -	Isolation from source to drain of a closed switch.

6.5 Logistic support. Lead materials and finishes (see 3.3) are interchangeable. Unless otherwise specified, microcircuits procured for Government logistic support will be procured to device class B (see 1.2.2), lead material and finish C (see 3.3). Longer length leads and lead forming shall not affect the part number.

6.6 Substitutability. The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification shall functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information shall not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-M-38510.

<u>Military device type</u>	<u>Generic-industry type</u>
01	5040
02	5041
03	5042
04	5043
05	5044
06	5045
07	5046
08	5047

Custodians:  
Army - ER  
Navy - EC  
Air Force - 17

Review activities:  
Army - ER, MI  
Navy - EC, SH  
Air Force - 11, 85, 99  
NASA - NA

User activities:  
Army - AR, SM  
Navy - AS, CG, MC, OS  
Air Force - 19

Preparing activity:  
Air Force - 17

Agent:  
DLA - ES

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